



Transmission Electron Microscopy (TEM)

CH-633 - Online edition

Introduction to transmission electron microscopy (TEM)

TEM imaging and diffraction

High-resolution TEM

Scanning TEM (STEM)

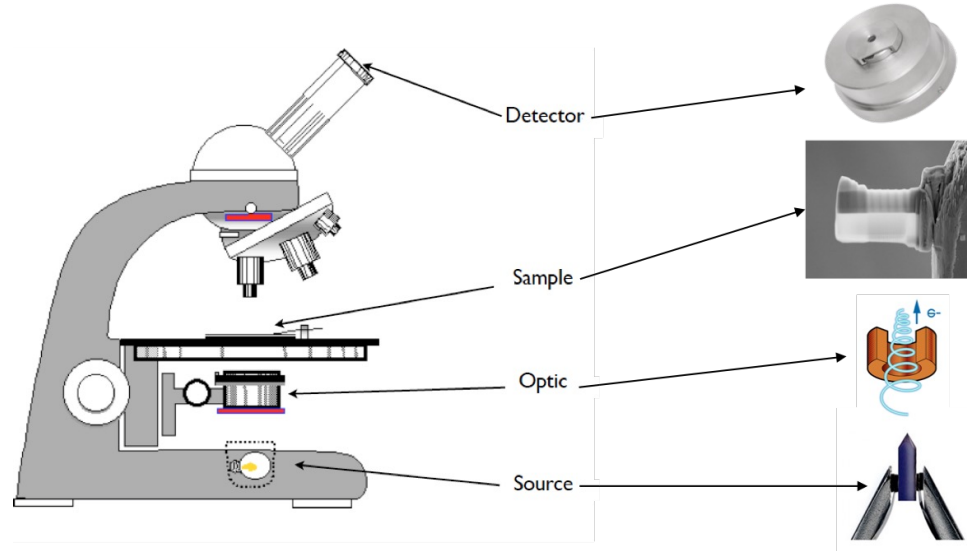
Analytical techniques

Energy-dispersive X-ray (EDX) analysis in STEM

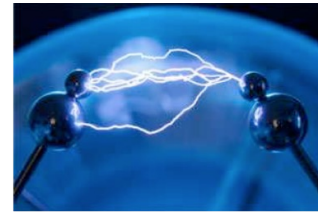
Electron energy-loss spectroscopy (EELS)

In situ TEM

Some examples and Summary

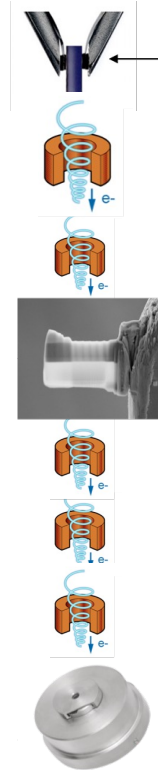
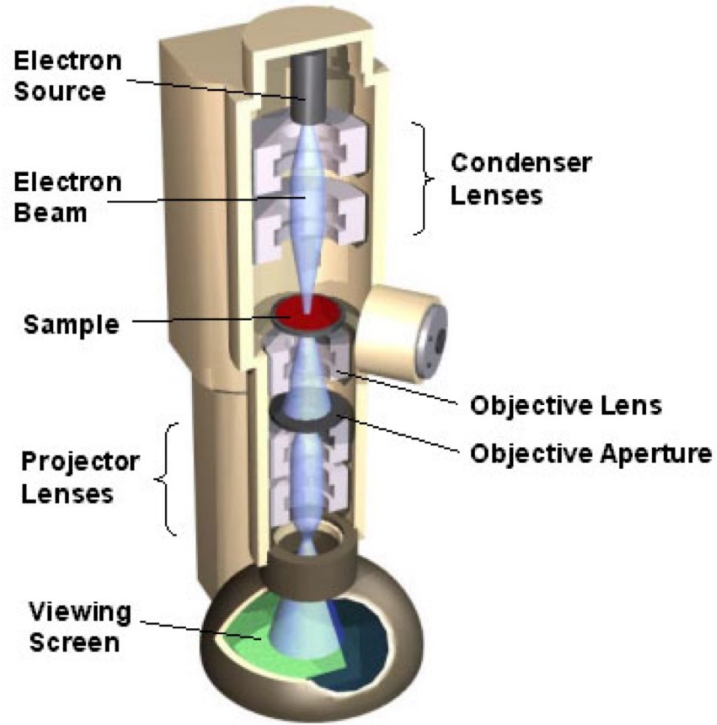


Visible light

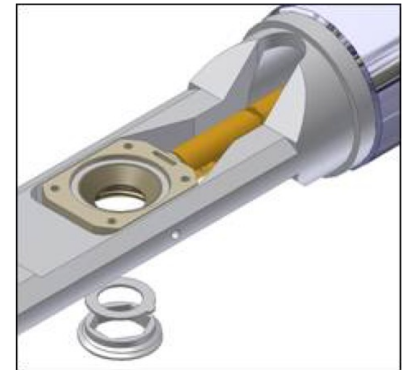
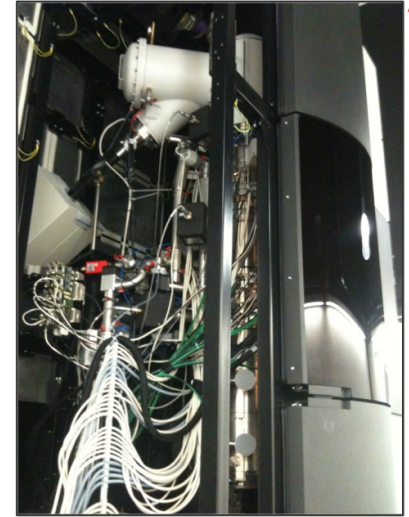


Fast electrons
100–300 keV
(0.5–0.8 c !)

Can consider analogous to projection light microscopy, but with better resolution



Double Cs-corrected FEI Titan-Themis @ CIME-EPFL



Specimen should be electron transparent:
several nanometers thick

Why fast electrons?

	Advantageous	Disadvantageous
Visible light	Not very damaging Easily focused Eye detector	Long wavelengths (400 nm)
X-rays	Small wavelength (Angstrom) Good penetration	Hard to focus Damage sample
Neutrons	Low sample damage Small wavelength (pm)	How to produce? How to focus?
Electrons	Small wavelength (pm) Can be focused to a sub-Å size probe Wave-particle duality	Damage sample Poor penetration (< x00 nm)

High energy electrons have a short wavelength (e.g. 2.5 pm @ 200 keV)

Easy to produce high brightness electron beams

Easy to manipulate: focused

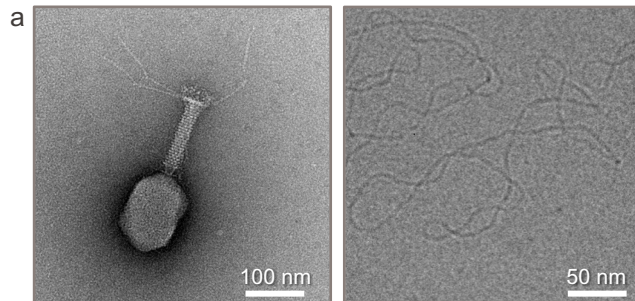
Interact strongly with matter

Electron microscopes are used not only for obtaining good resolution images but also:

- **can be used as a diffractometer**
- **for chemical analyses (EDX and EELS)**
- **for imaging/measuring electric-, magnetic-, or strain-field in the sample**
- **for measuring optoelectronic properties (e.g. cathodoluminescence), ...**

***Aberrations & instabilities → Actual resolution around 25-50 Å, but atomic/sub-Å resolution possible in TEM**

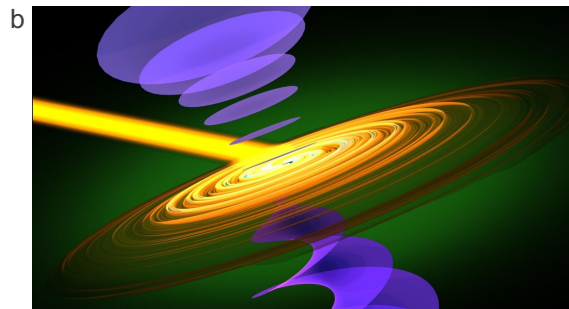
Biology and life science

T4 virus ^a

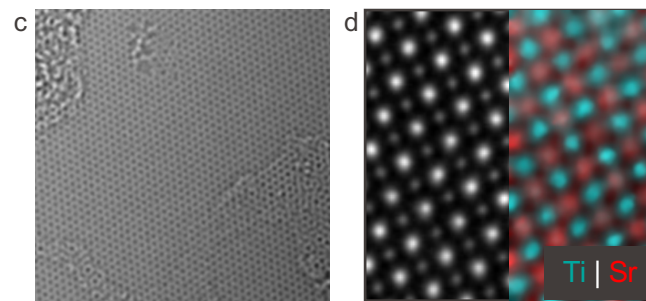
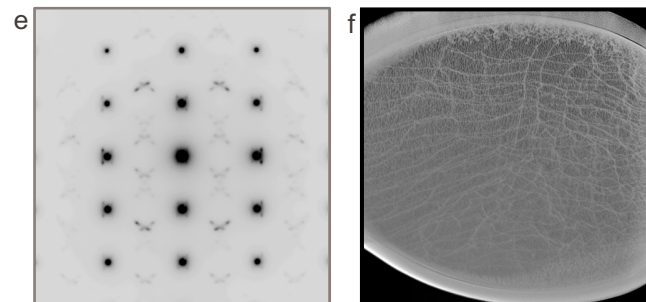
A bacteriophage that infects Escherichia coli bacteria

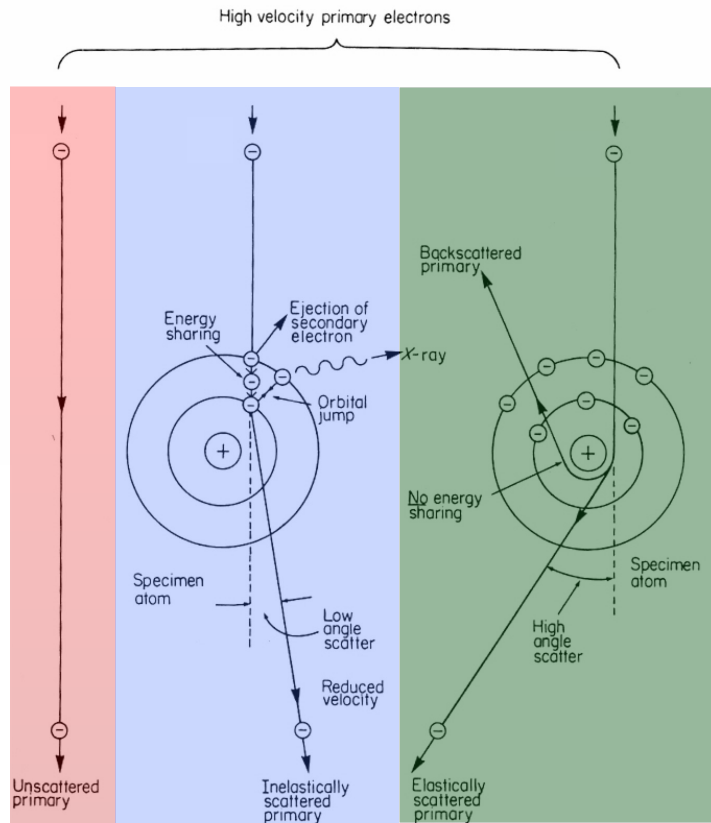
DNA molecule ^a

Fundamental physics

Ultrafast electron vortex beams ^b

Chemistry & materials research

Imaging and spectroscopy at atomic resolution ^{c,d}Crystallographic studies ^eAnalyzing crystal defects ^f^a Images courtesy of Dr. D. Demurtas, CIME-EPFL.^b Vanacore et al., Nature Materials (2019).^c Huang et al., Nat. Comm. 2018.^d Oveisi et al., Ultramicroscopy (2017).^e Oveisi et al., Scripta Mat. (2013).^f Bencan et al., Nat. Comm. (2021).



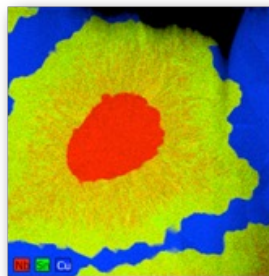
Inelastic events: The result is a **transfer of beam energy** to the specimen atom (**energy loss**) and a potential expulsion of an electron from that atom as a **secondary electron (SE)**.

If the vacancy due to the creation of a secondary electron is filled from a higher level orbital, an X-Ray or Auger characteristic of that energy transition is produced.



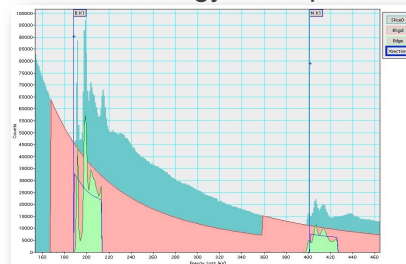
That's why TEMs are shielded!

Characteristic X-rays

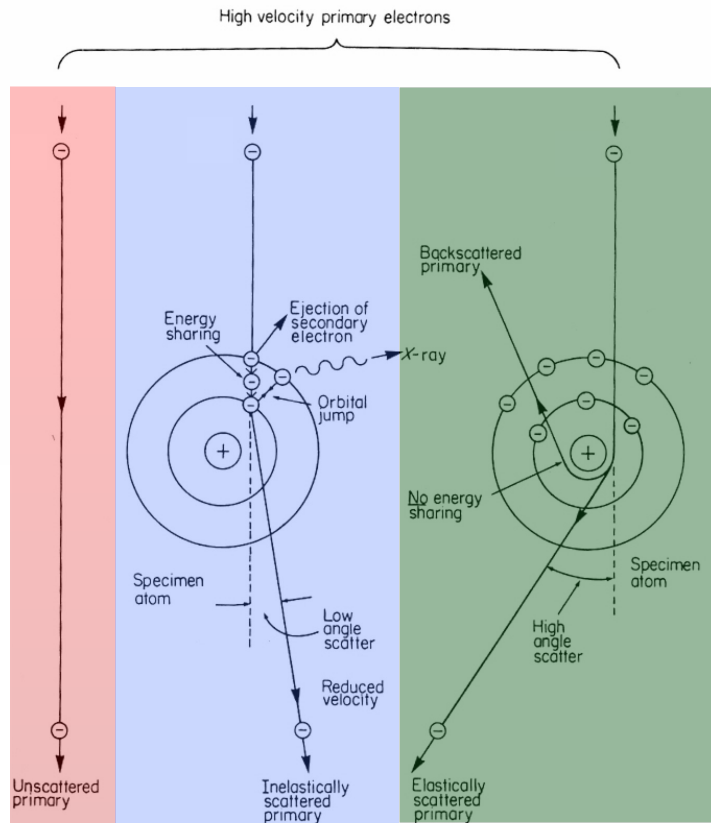


Chemical composition

Electron energy-loss spectrum



Chemical composition, band-gap & optical properties

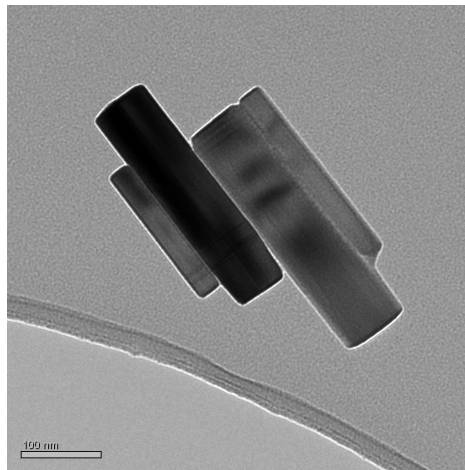


Elastic events occur when a beam electron interacts with the electric field of the nucleus or electron cloud of a specimen atom (Coulomb forces), resulting in a change in the direction of the beam electron **without a significant change in the energy** of the beam electron (< 1 eV).

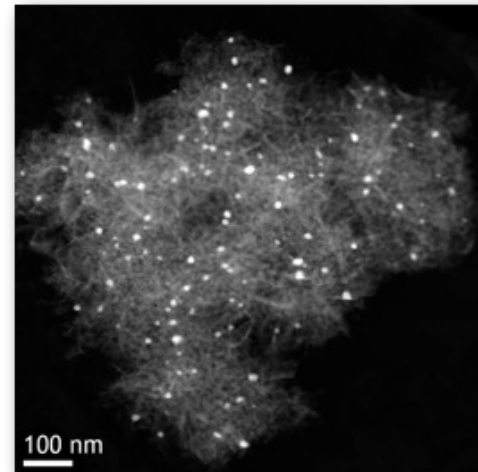
Coulombic interaction within the electron cloud, Low-angle scattering
Coulombic attraction by the nucleus, Higher-angle scattering

Thicker specimen or larger nucleus $\rightarrow$ More scattering

GaN nano wires



Mass/thickness contrast
Bright-field TEM image

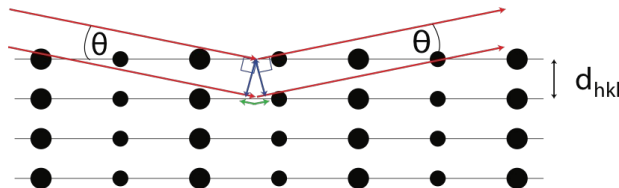


Mass/thickness contrast
HAADF-STEM image

Pt catalyst particles on Al_2O_3

e^- as wave & Bragg scattering

For X-ray diffractometer



X-ray scattering:

Path difference between reflection
from planes distance d_{hkl} apart
 $= 2d_{hkl} \sin\theta$

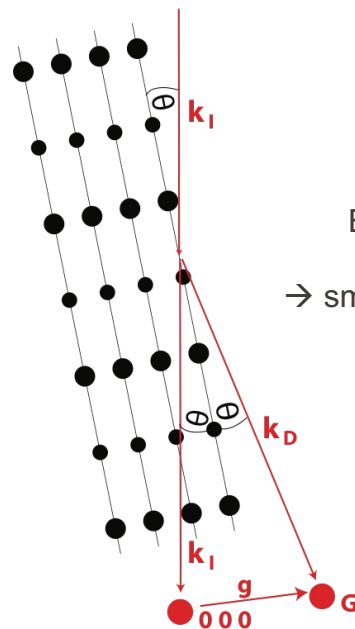
Bragg law

$$n\lambda = 2d_{hkl} \sin\theta$$

or

$$\lambda = 2d_{hknkl} \sin\theta$$

For TEM electrons come from top, but
otherwise geometrically the same

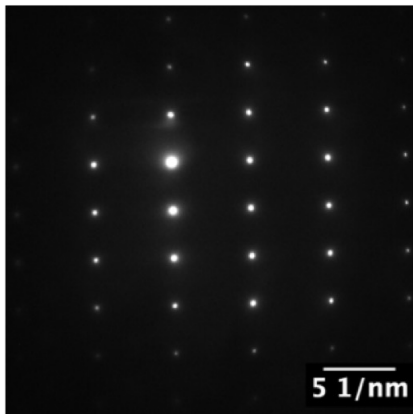


Electron diffraction: $\lambda \sim 0.001$ nm
therefore: $\lambda \ll d_{hkl}$

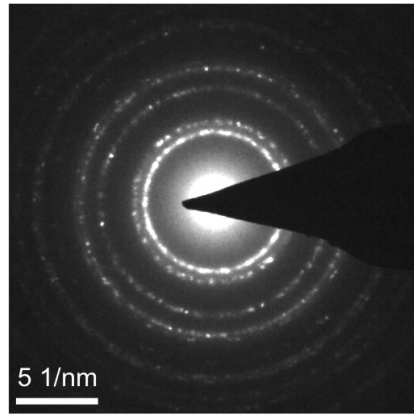
→ small angle approximation: $\lambda \approx 2d_{hknkl} \theta$

→ Bragg diffraction at angle 2θ

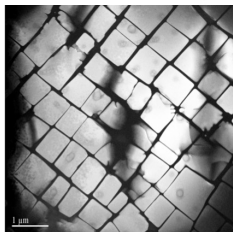
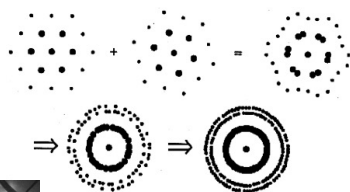
Electron diffraction pattern



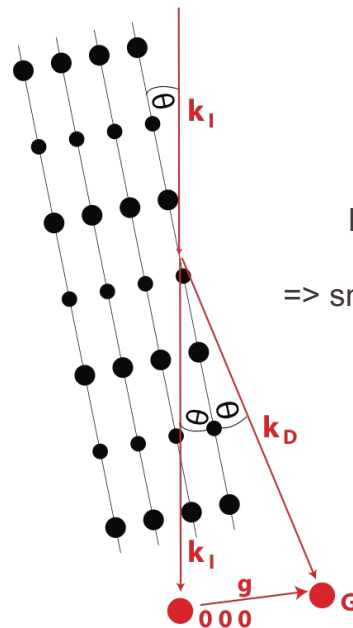
Spot pattern from a single crystal
Spots represent different (hkl) planes



Ring pattern as many crystallites oriented
differently in diffraction conditions



Therefore TEM gives image & diffraction!



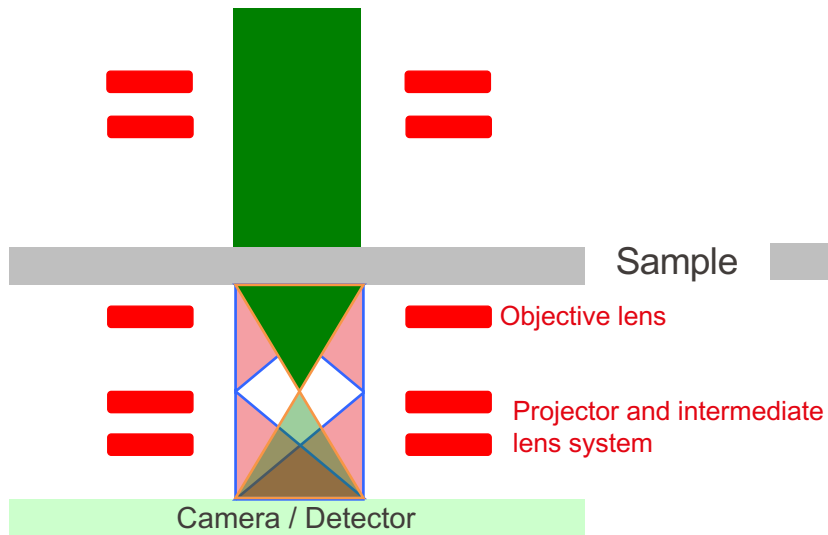
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$\Rightarrow$ small angle approximation: $\lambda \approx 2d_{hkl}\sin\theta$

$\Rightarrow$ Bragg diffraction at angle 2θ

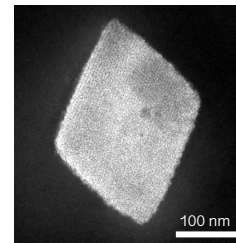
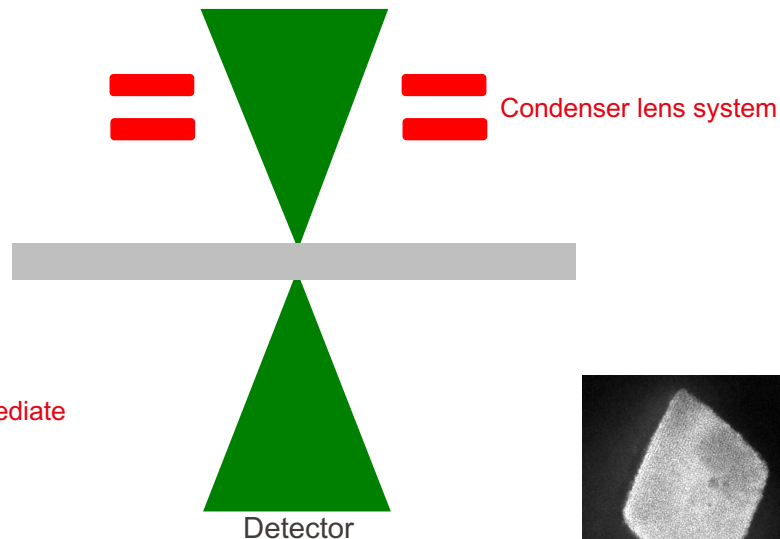
Conventional TEM

Electron beam (60-300 keV)

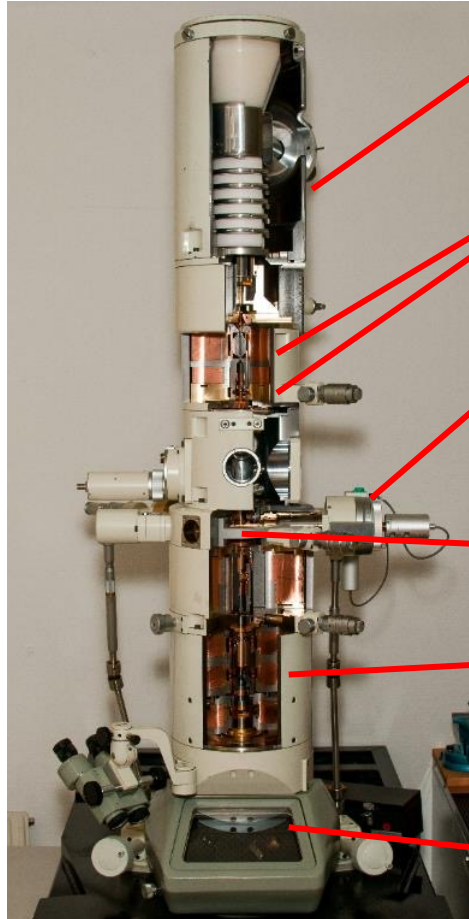


Scanning mode (STEM)

Electron beam (30-300 keV)



2D projection of a 3D object

**Electron Source**

Produces high energy, large current, and high coherence electron beams necessary for generating diffraction patterns and high spatial resolution images

Condenser system and condenser aperture

Controls spot size and illumination area on sample (beam intensity)

Specimen holder and goniometer**Objective lens and objective aperture**

Images sample and is the strongest lens in the system

Intermediate and projector lenses

Changes modes from diffraction to imaging
Controls magnification

Detectors / Camera

Various different configurations designed to collect signals produced by the high-energy electron beam

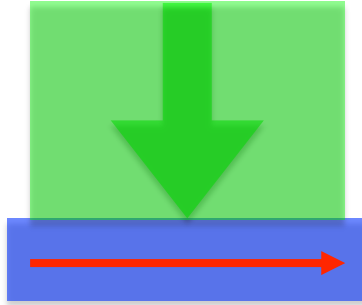
■ Image formation in TEM

- Image and diffraction modes
- Bright- and dark-field modes
- High-resolution TEM

■ Image contrast in TEM

- Mass-thickness contrast
- Diffraction contrast
- Phase contrast

Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$



Sample (thin,
 e^- transparent)

←—————→ Objective lens



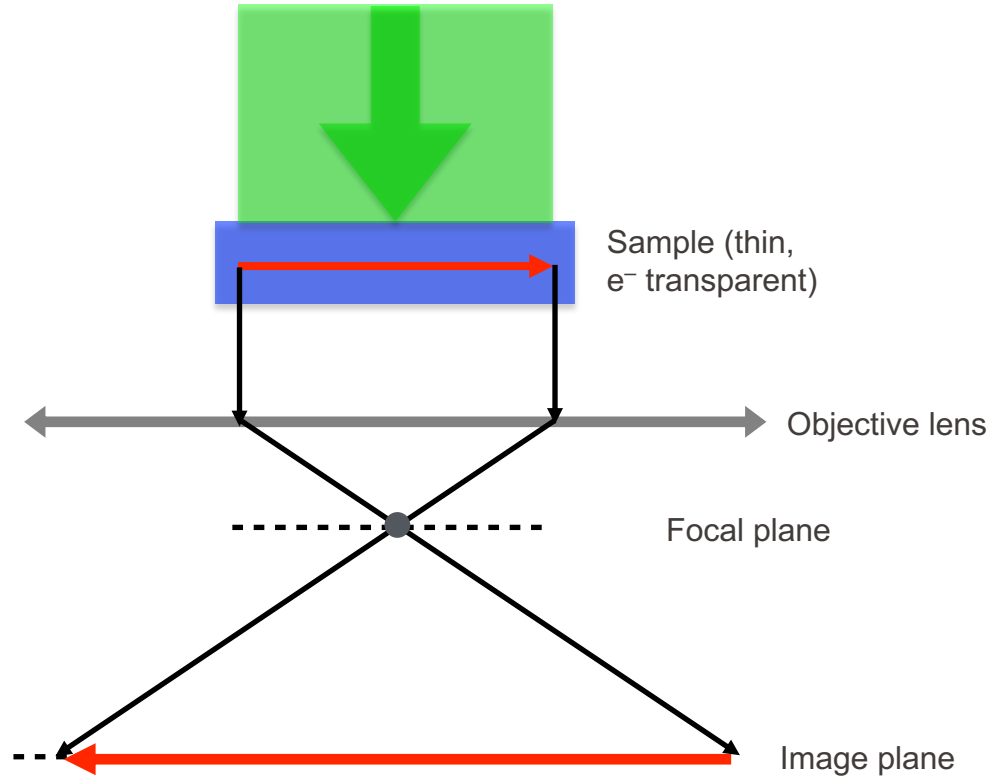
Focal plane



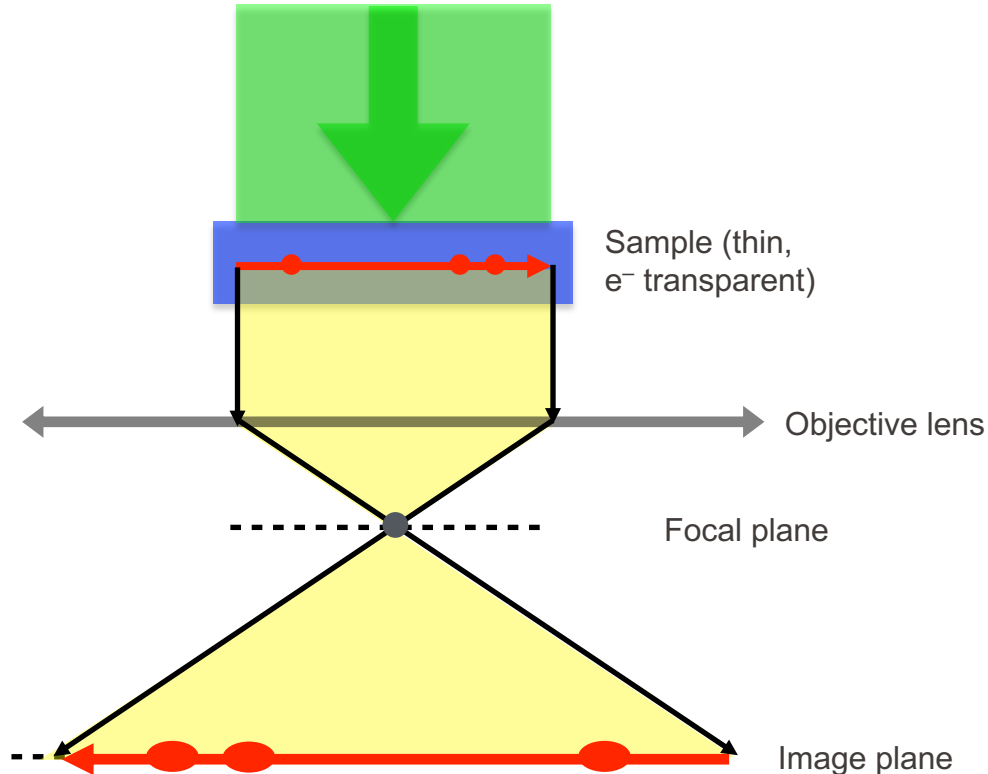
Image plane



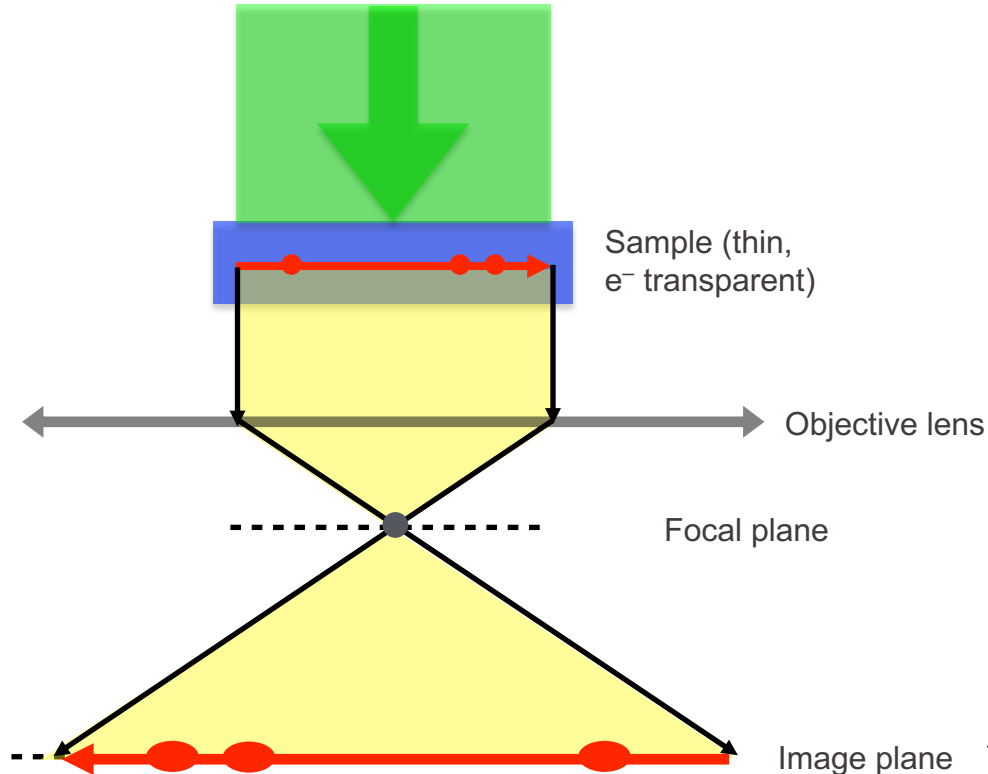
Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$



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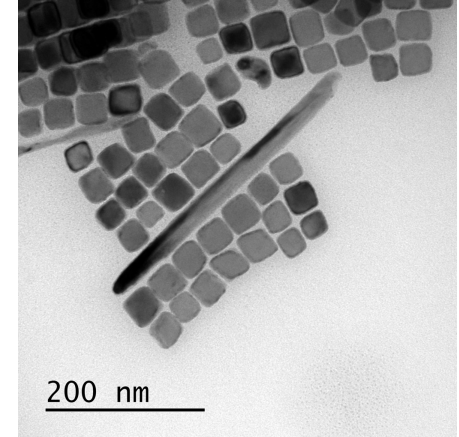


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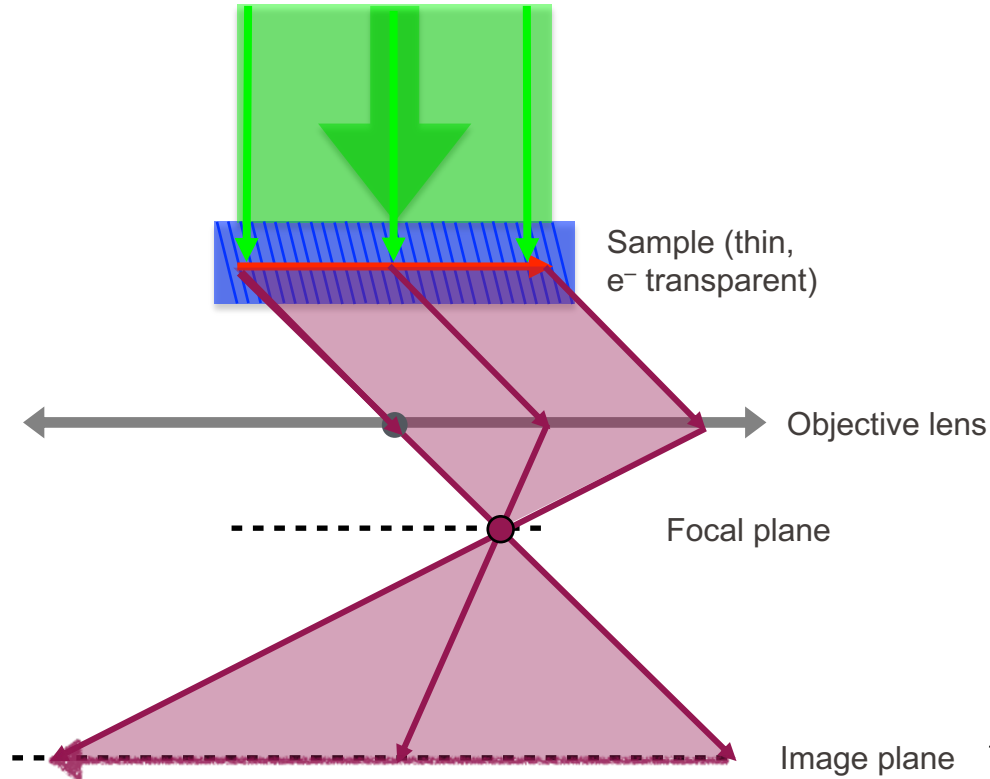
Why some cubic particles appear darker than others?

Cubic particles ($\approx 40 \text{ nm}$) of Cu

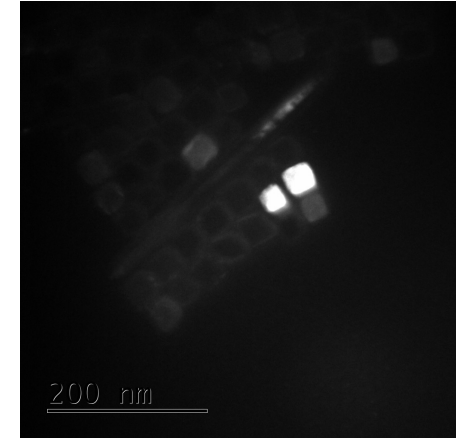
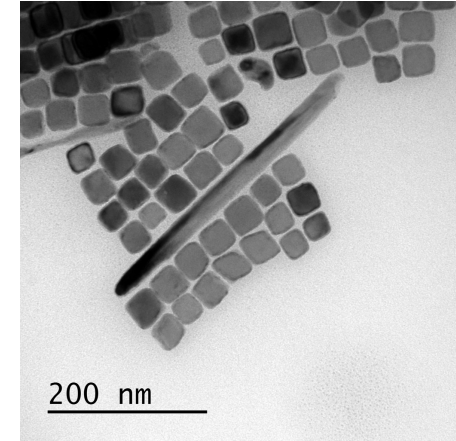


Bright-field image:
made by directly transmitted electrons

Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

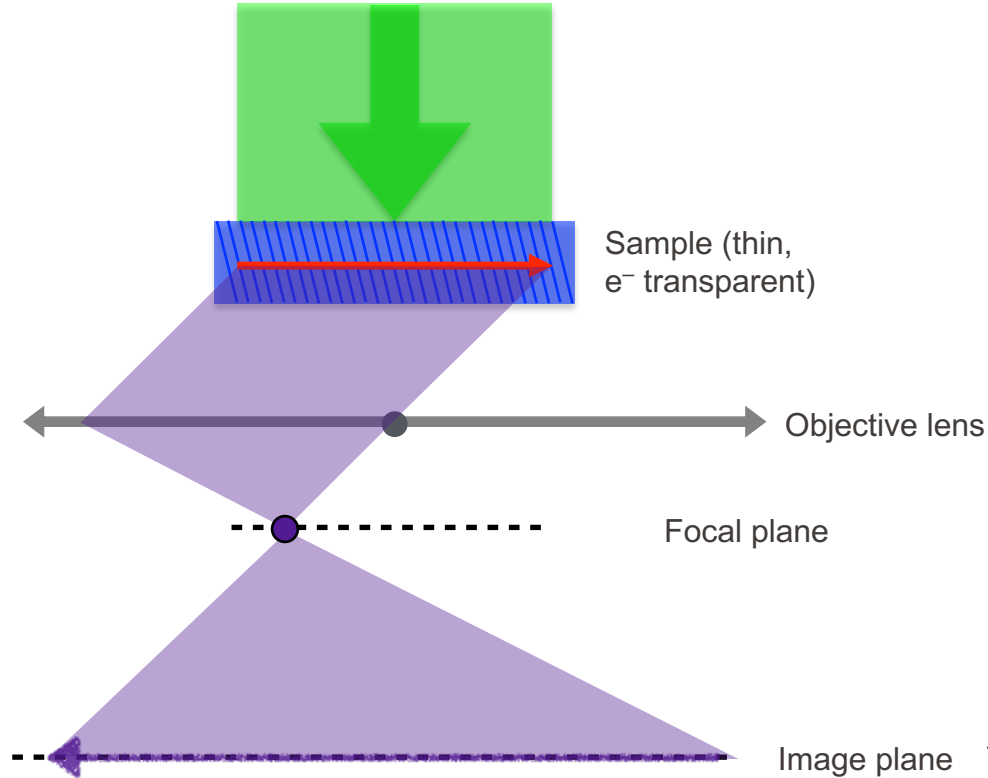


Bright-field image

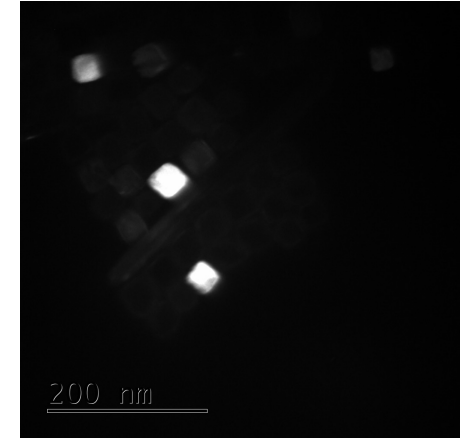
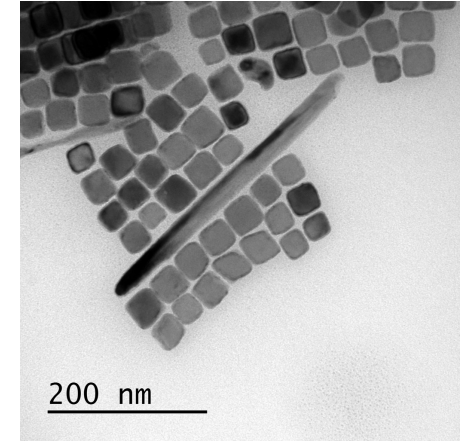


Dark-field image:
made by selected diffracted electrons

Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

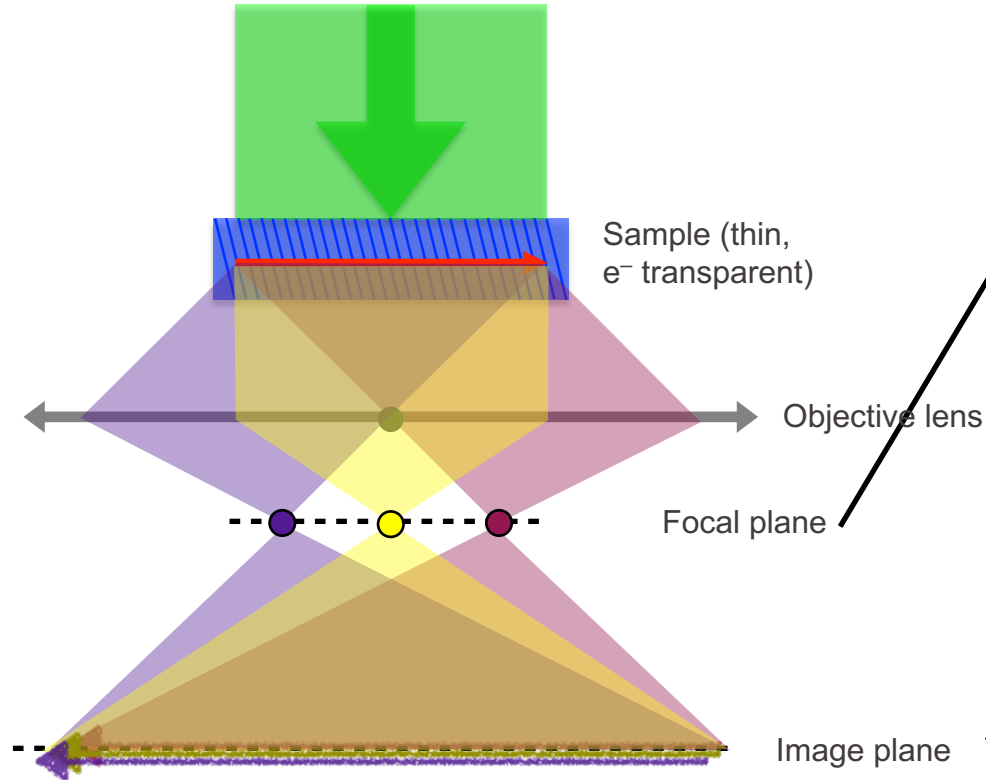


Bright-field image

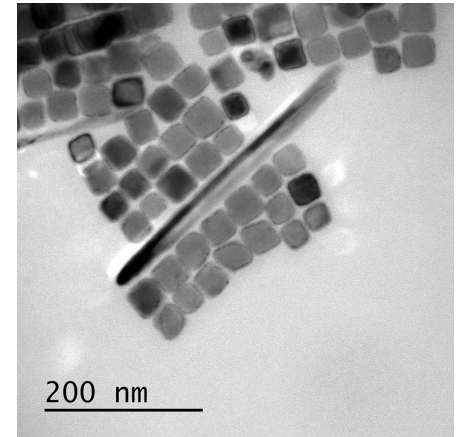
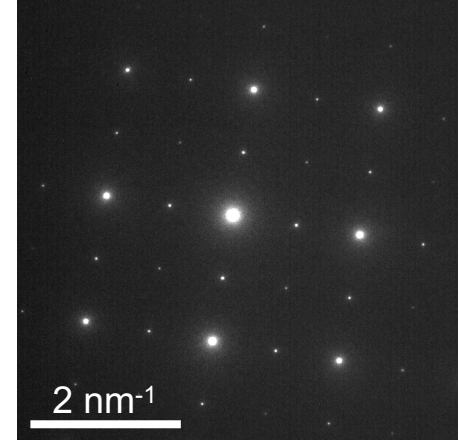


Dark-field image:
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Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

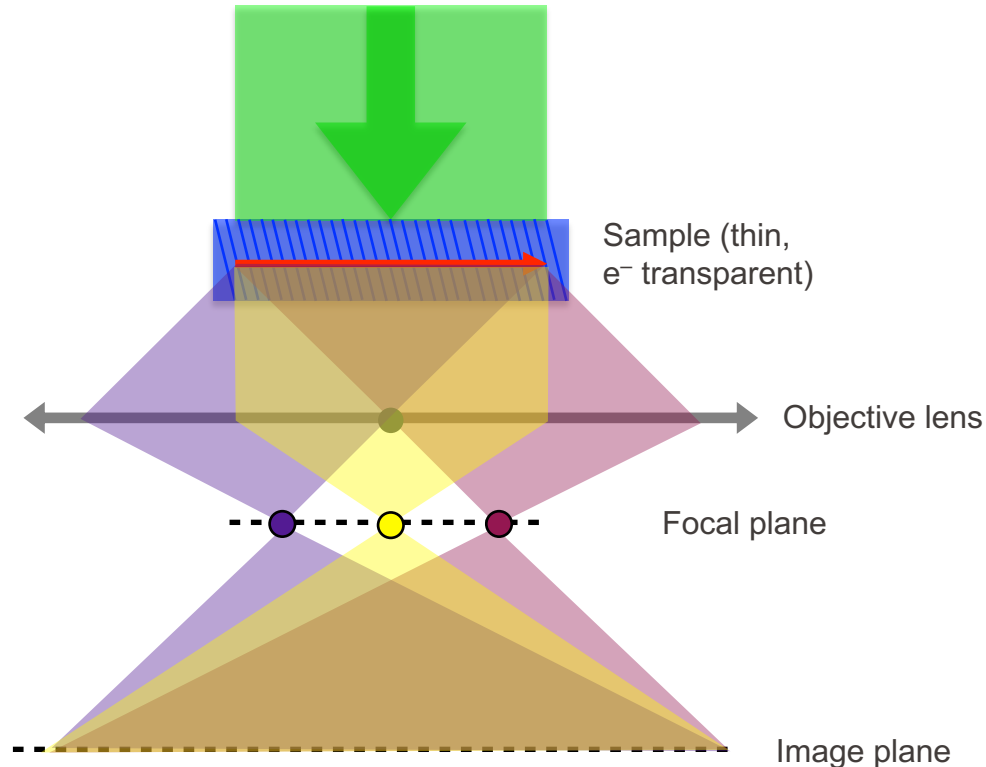


Electron diffraction pattern

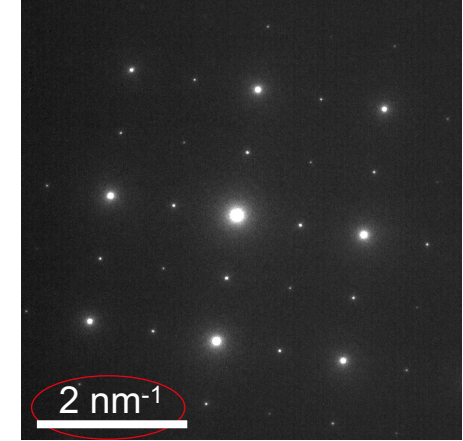


Ghost image:
Superposition of images made
by direct and diffracted electrons

Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

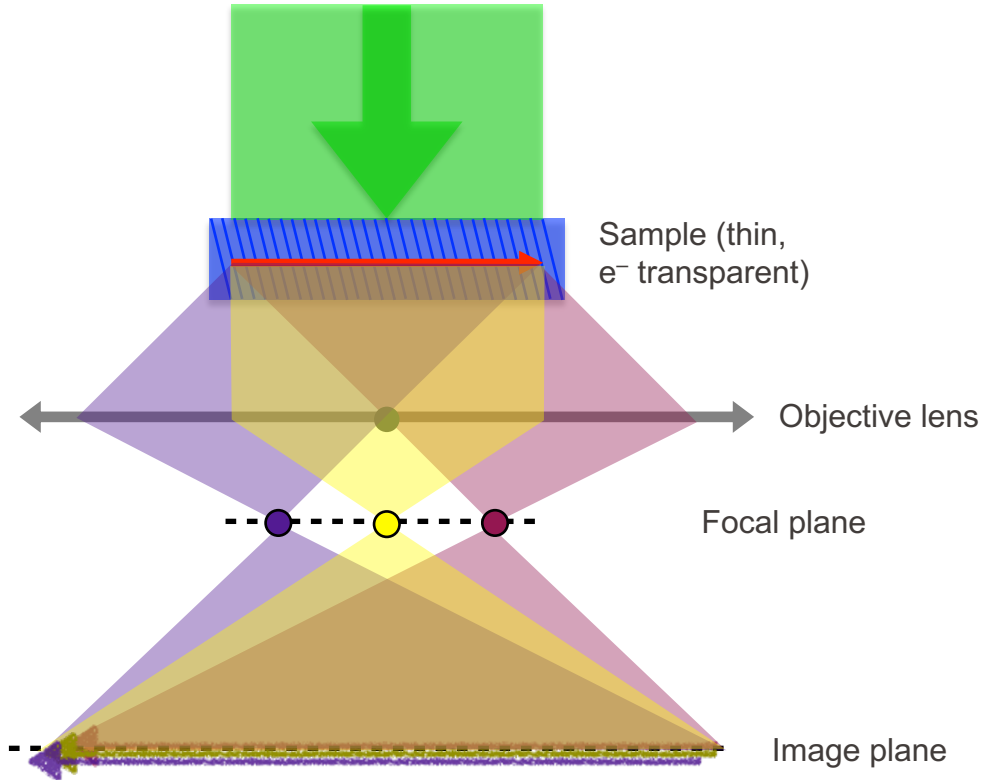


Electron diffraction pattern

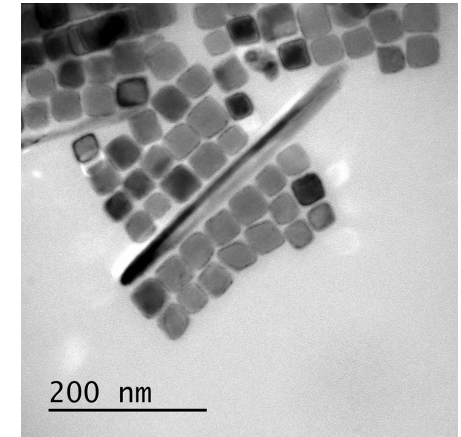
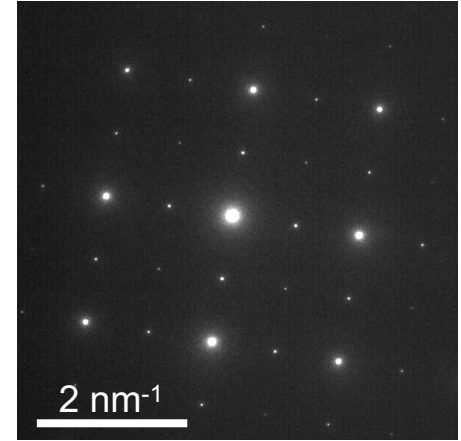


- *In back focal plane of objective lens parallel rays focused to point*
- *Diffraction – coherent scattering – creates sets of parallel rays from different crystal planes*
- *Focusing of these parallel rays in back focal plane creates spots of strong intensity:
the diffraction pattern*

Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

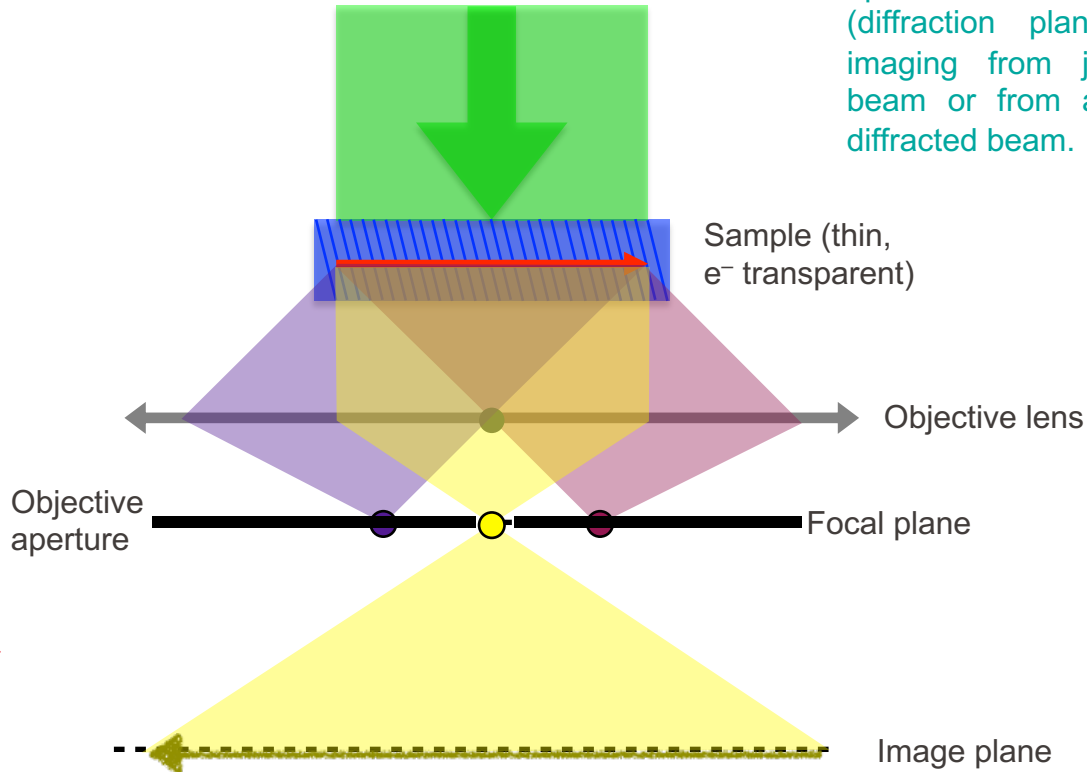


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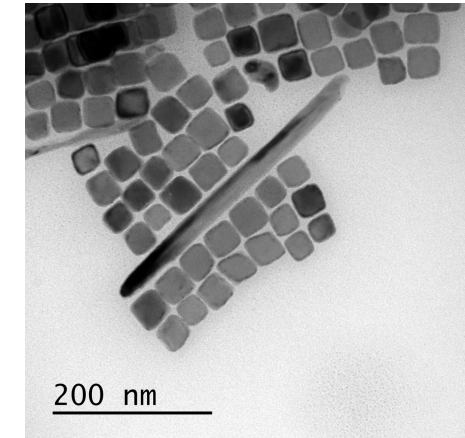
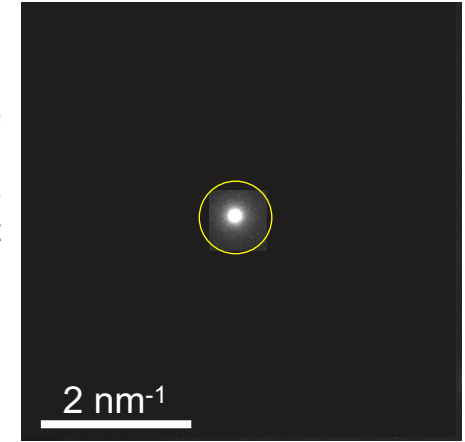


Parallel incident e^- beam; $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

Insertion of the “objective aperture” in focal plane i.e. (diffraction plane) allows imaging from just direct beam or from a selected diffracted beam.



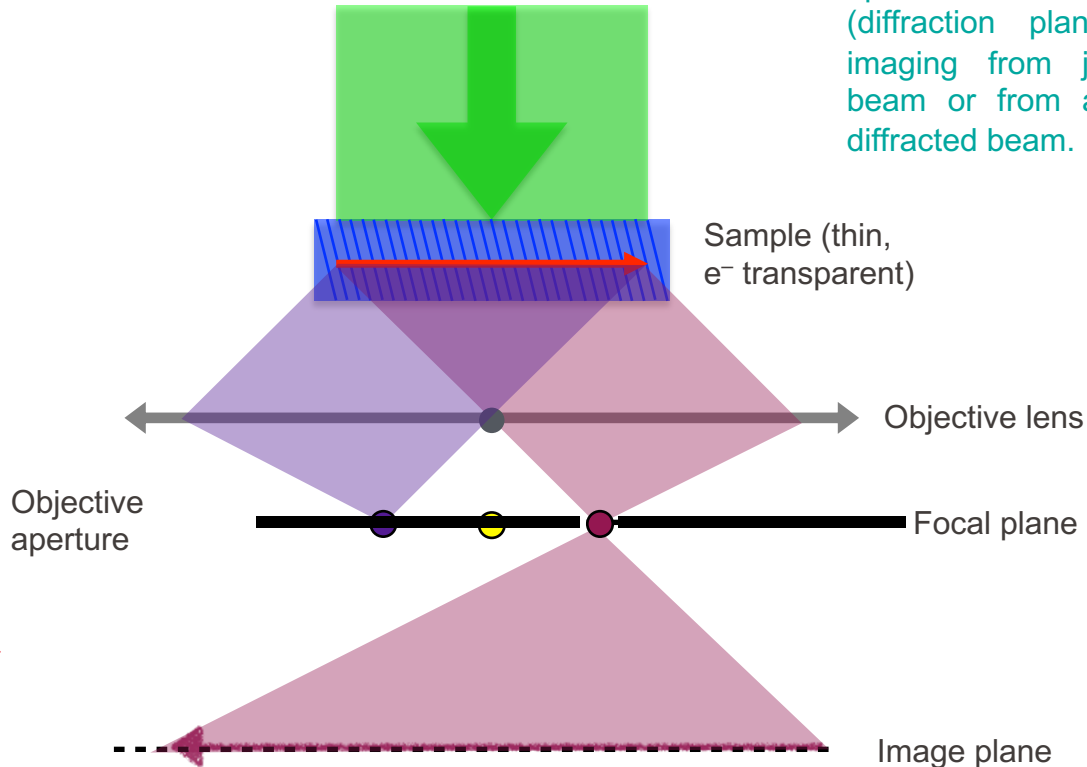
Electron diffraction pattern



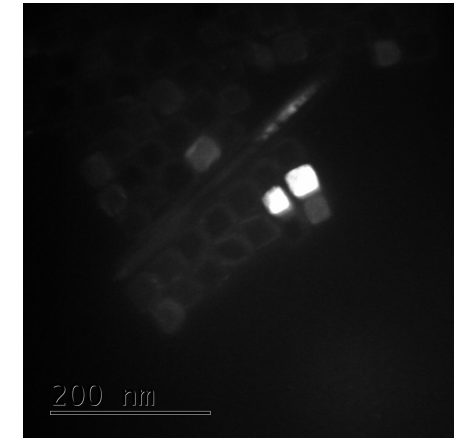
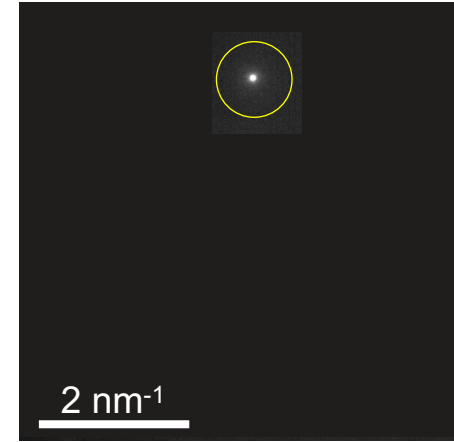
Bright-field image:
made by directly transmitted electrons

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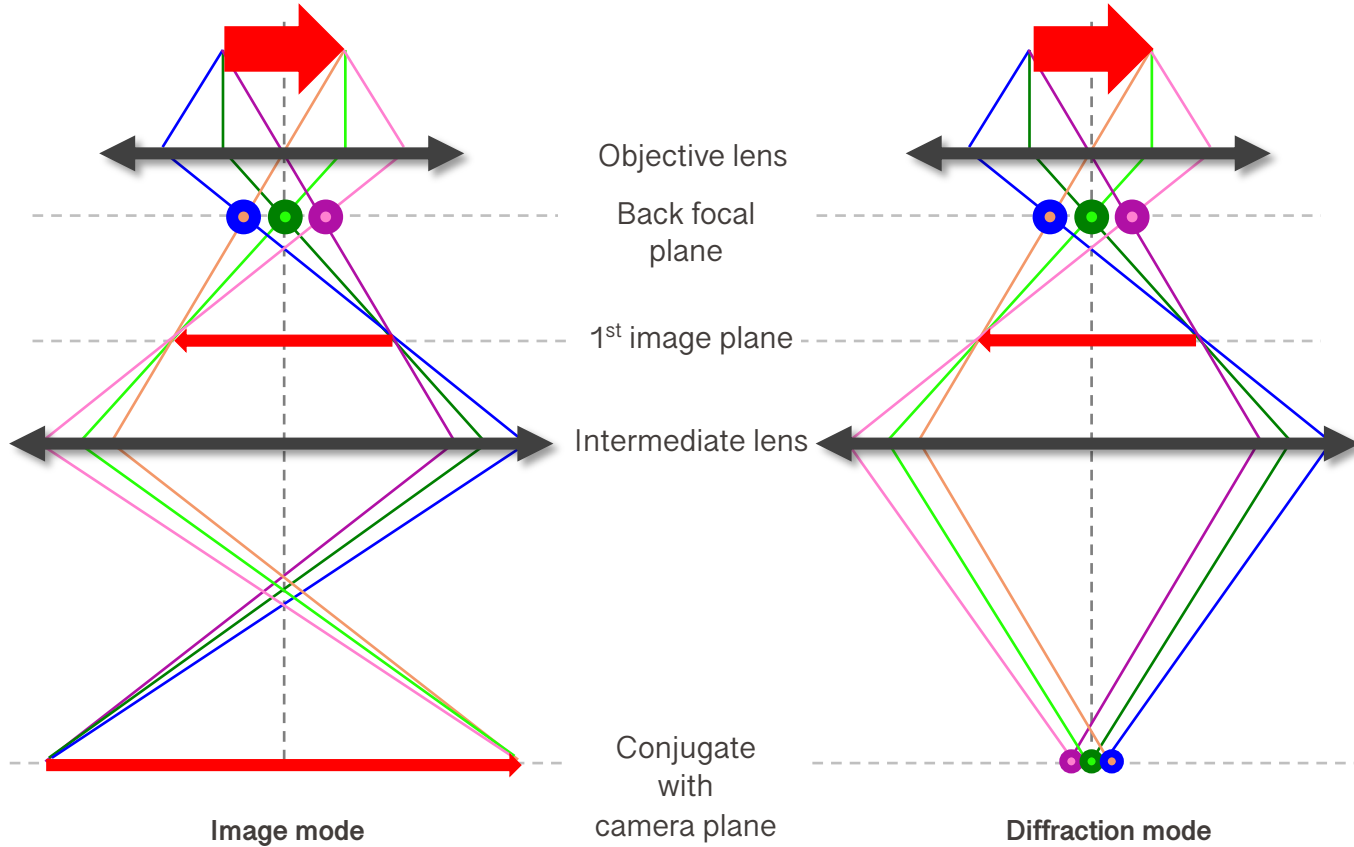
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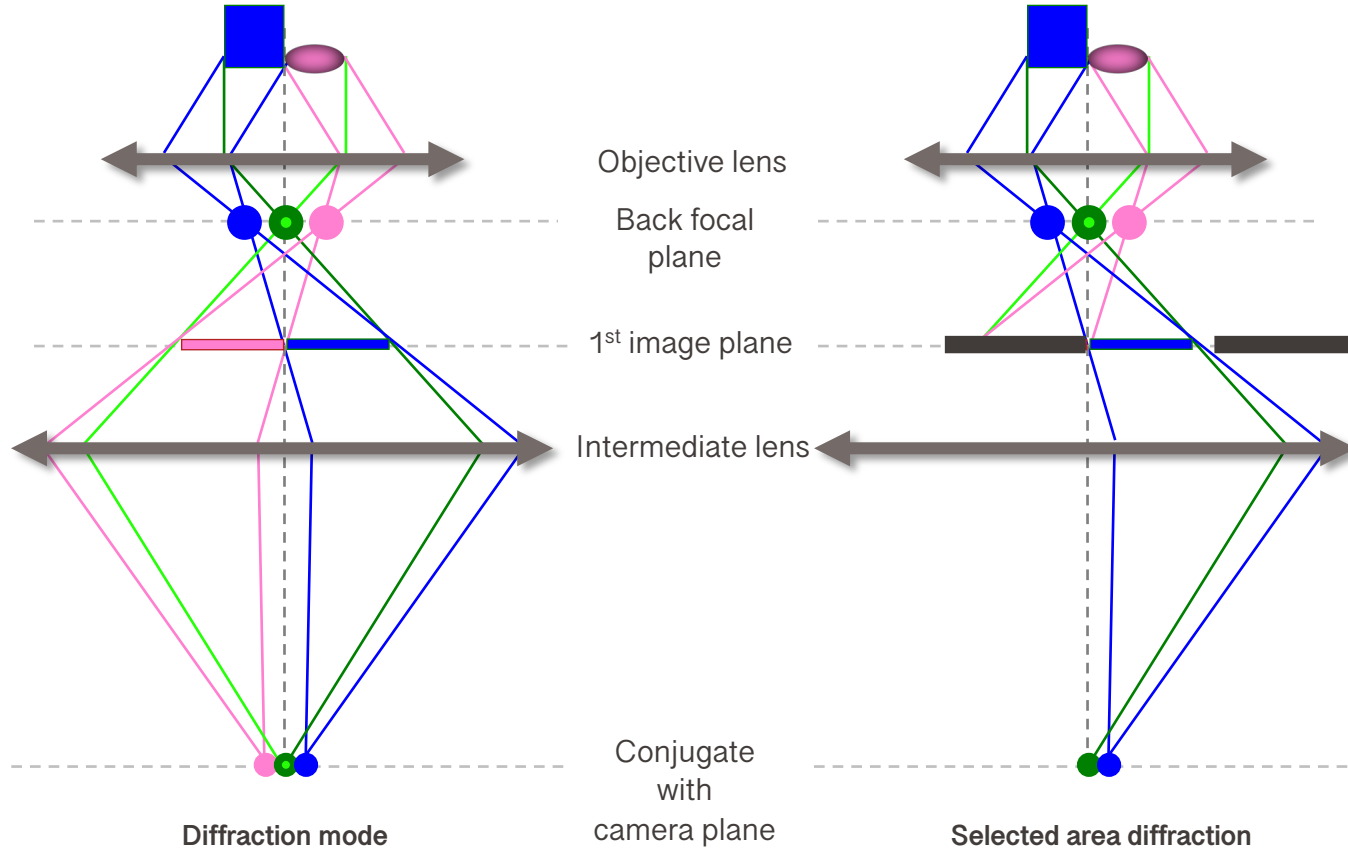


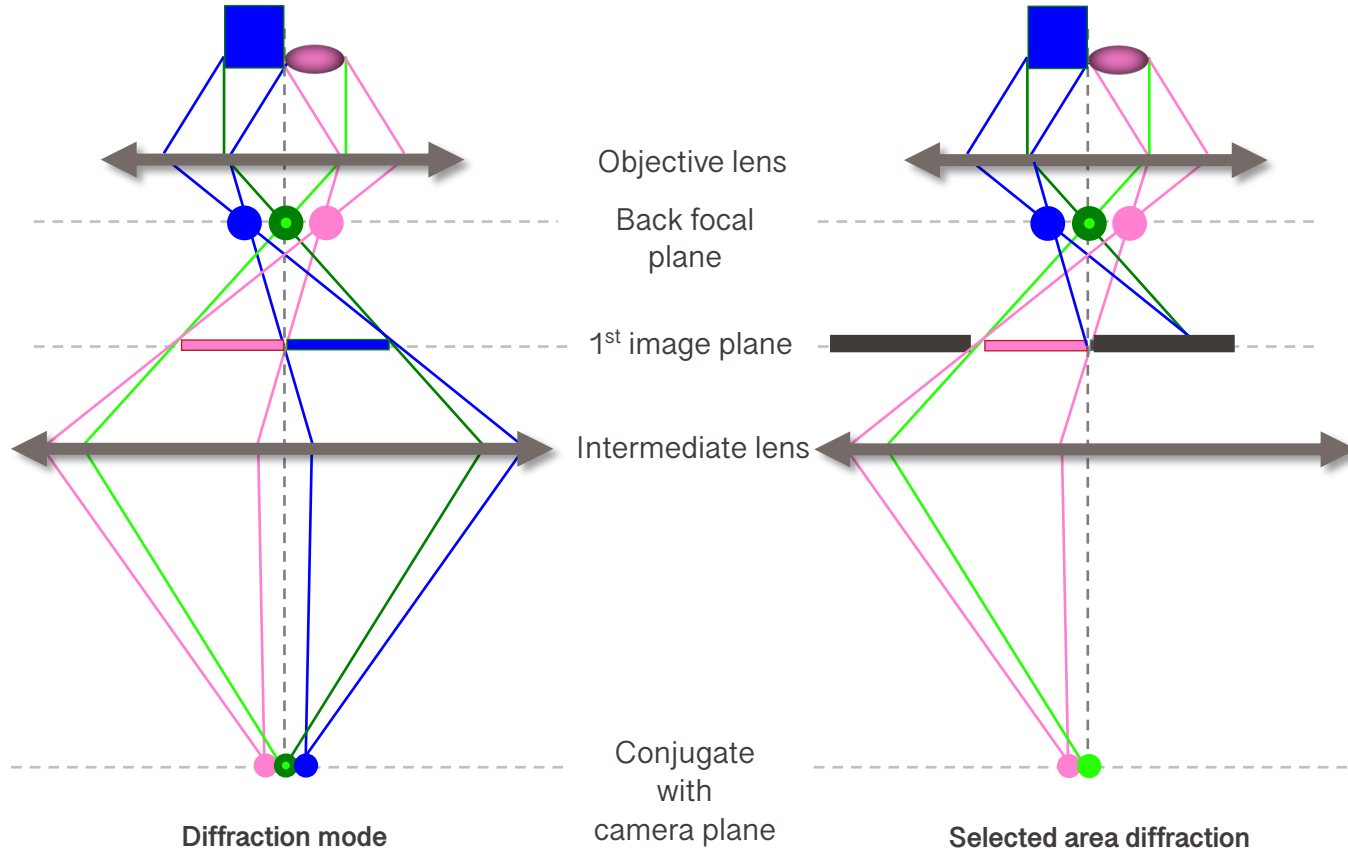
Electron diffraction pattern

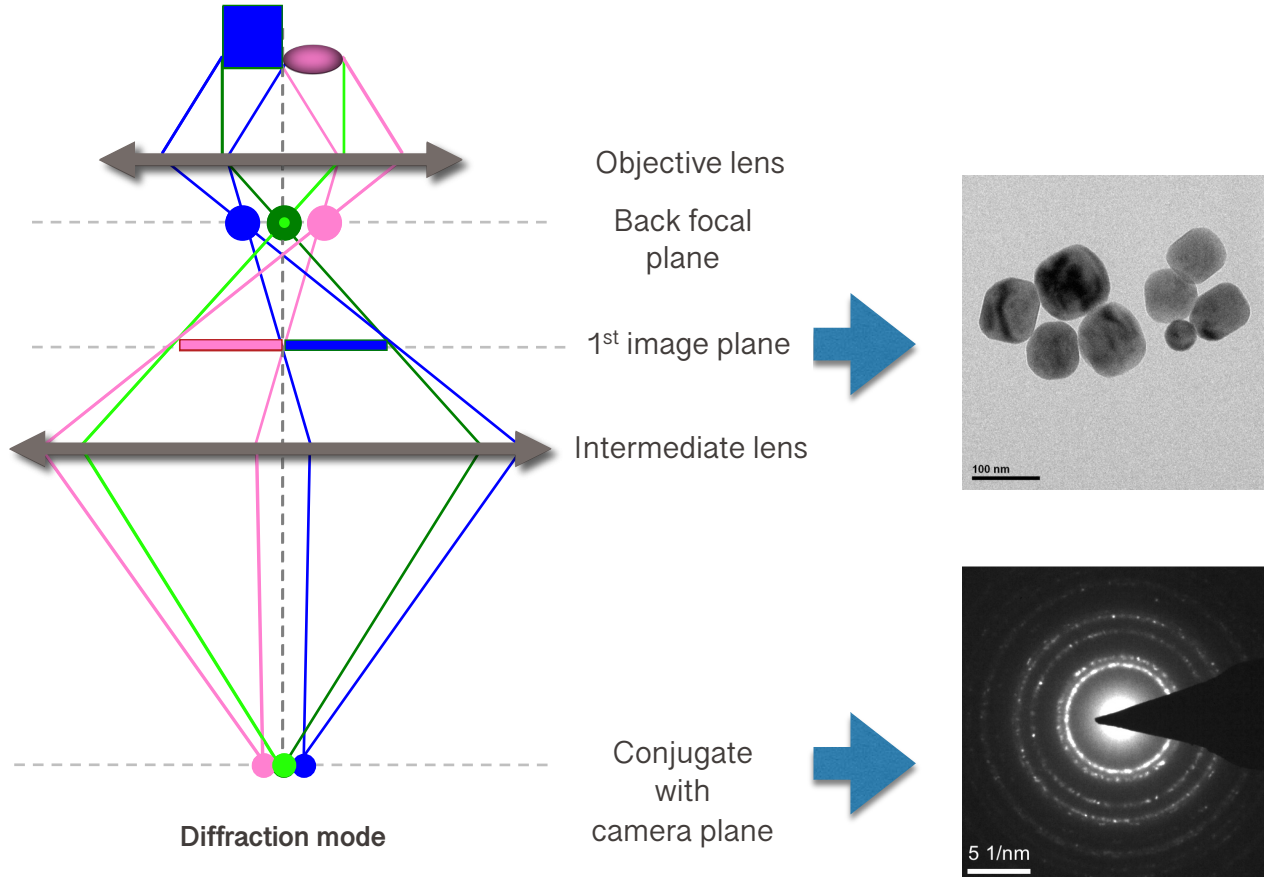


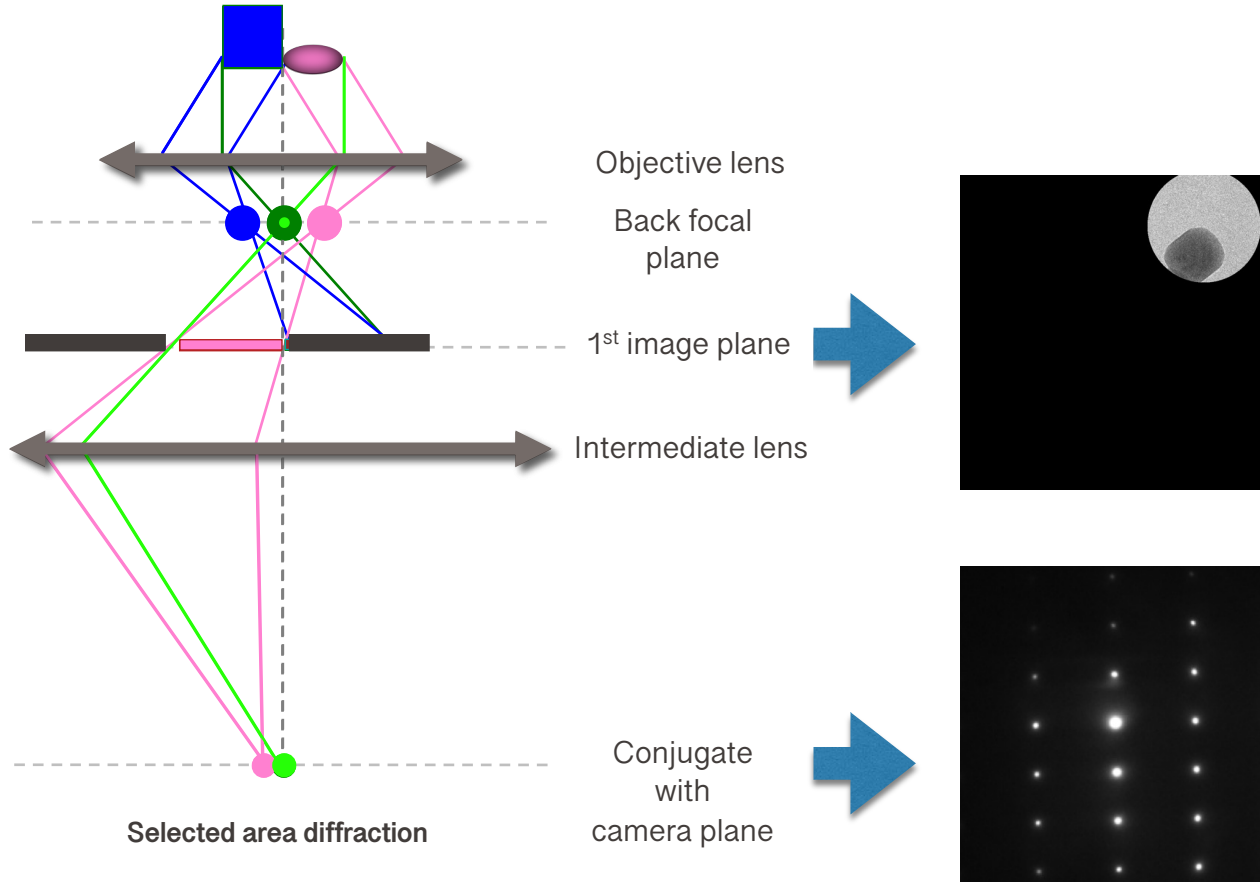
Dark-field image:
made by selected diffracted electrons

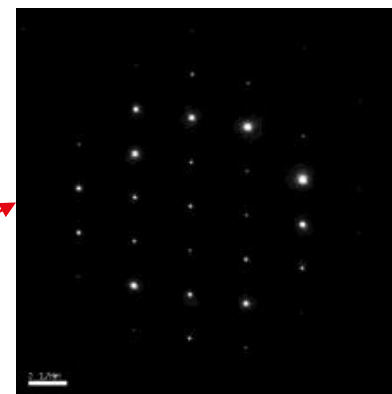
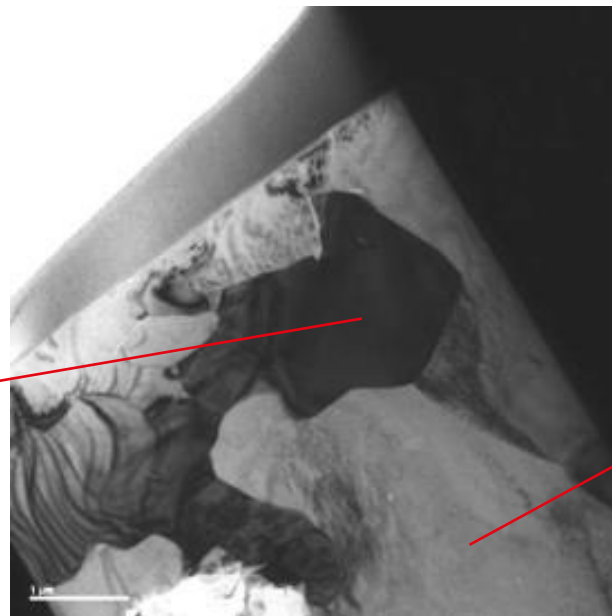




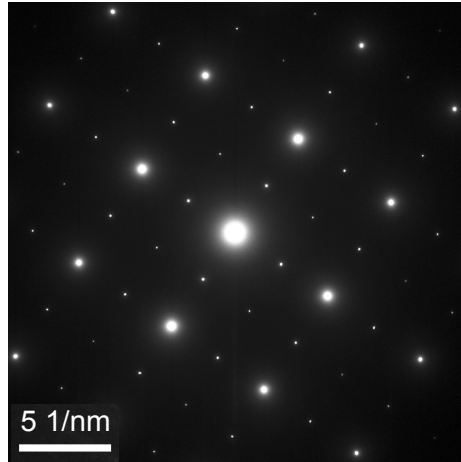






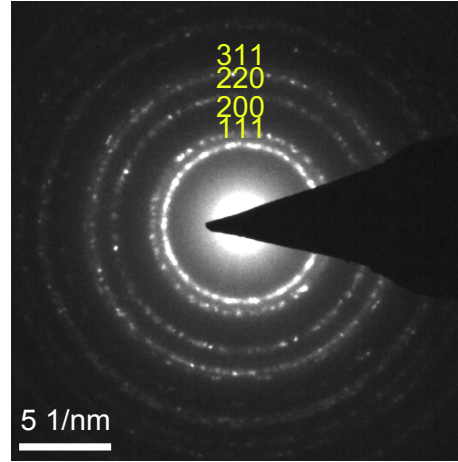
Monoclinic Al_3Fe Hexagonal $\gamma\text{-(AlFeSi)}$

Monocrystal



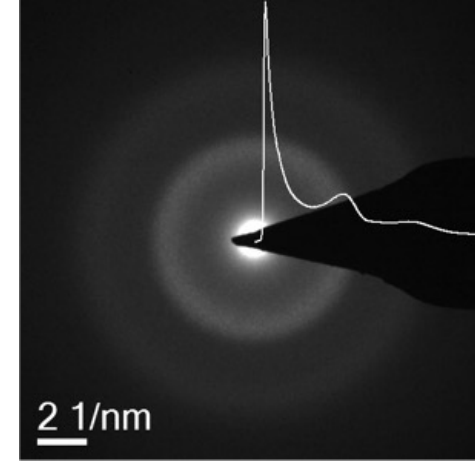
Oriented along a zone axis many (hkl) plans in diffraction conditions. Spot represent different (hkl) planes.

Polycrystalline

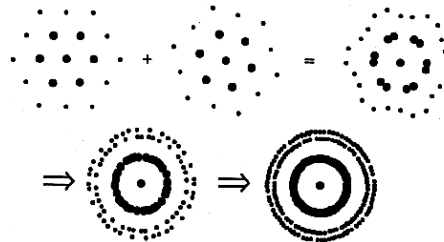


Ring pattern as many crystallites oriented differently in diffraction conditions. Each ring represents one family of {hkl} planes

Amorphous



Diffuse ring due to short-range order as interatomic distance $\sim$ constant
Radial distribution function

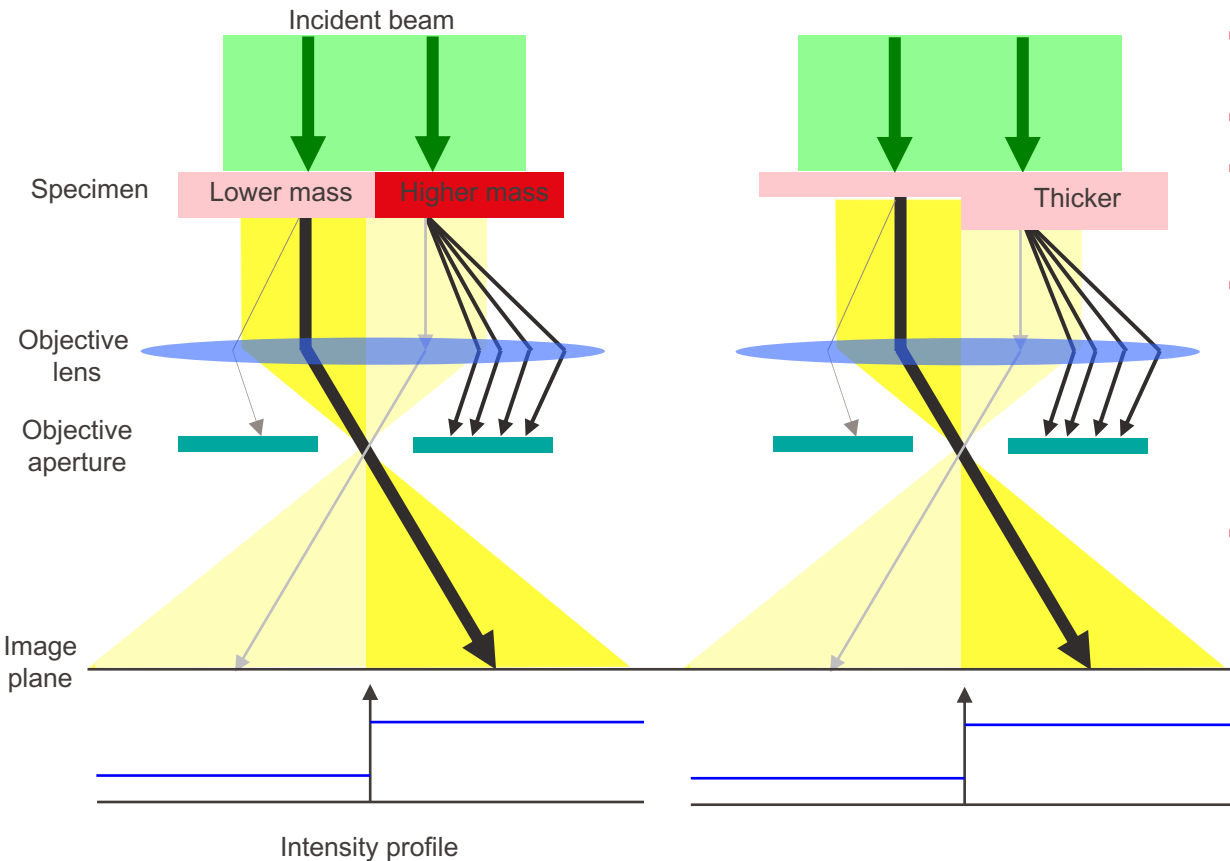


■ Image formation in TEM

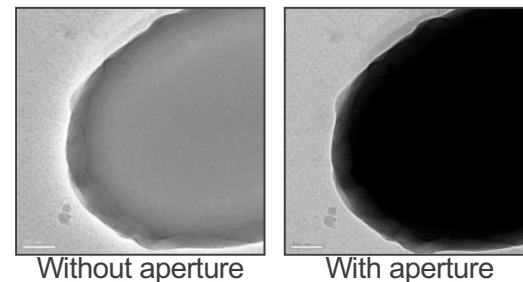
- Image and diffraction modes
- Bright- and dark-field modes
- High-resolution TEM

■ Image contrast in TEM

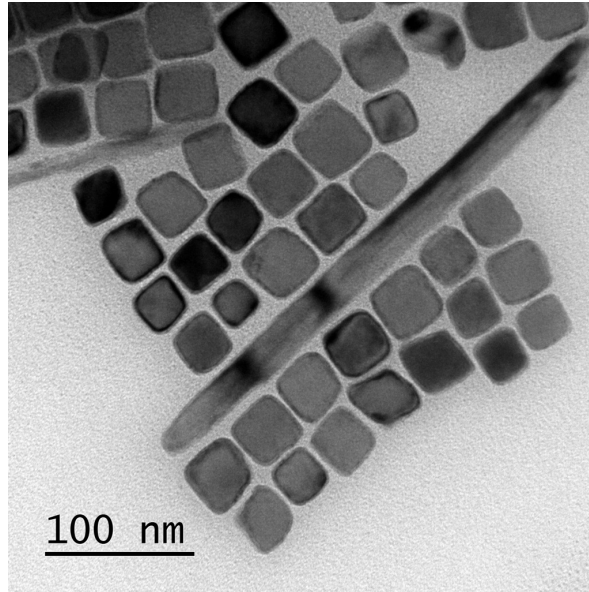
- Mass-thickness contrast
- Diffraction contrast
- Phase contrast



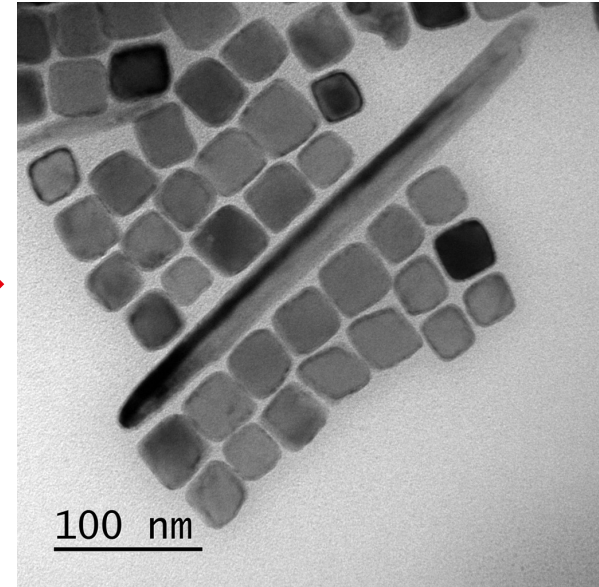
- Areas of higher mass/thickness scatter electrons more than others.
- Electrons are captured by the aperture.
- Areas of higher mass/thickness will therefore appear dark in the image formed by the direct beam.
- This is known as:
 - **mass thickness contrast,**
 - **scattering contrast,**
 - **aperture contrast or**
 - **amplitude contrast!**
- Applies to both Crystalline and Amorphous materials.



Example: Copper nano particles

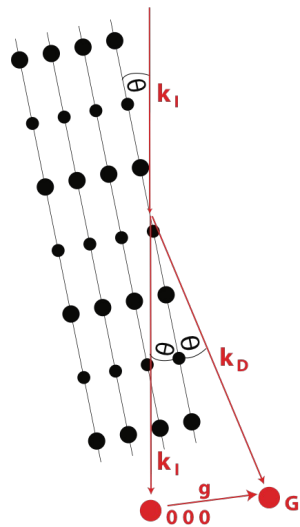


Tilting the sample



Why some of cubic particles appear darker than others?

Note that contrast changes when tilting the specimen

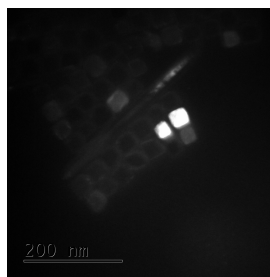
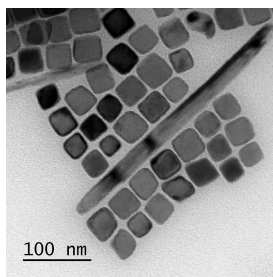
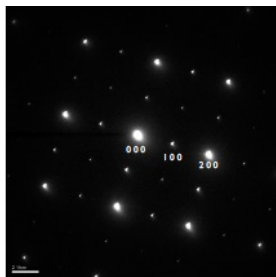
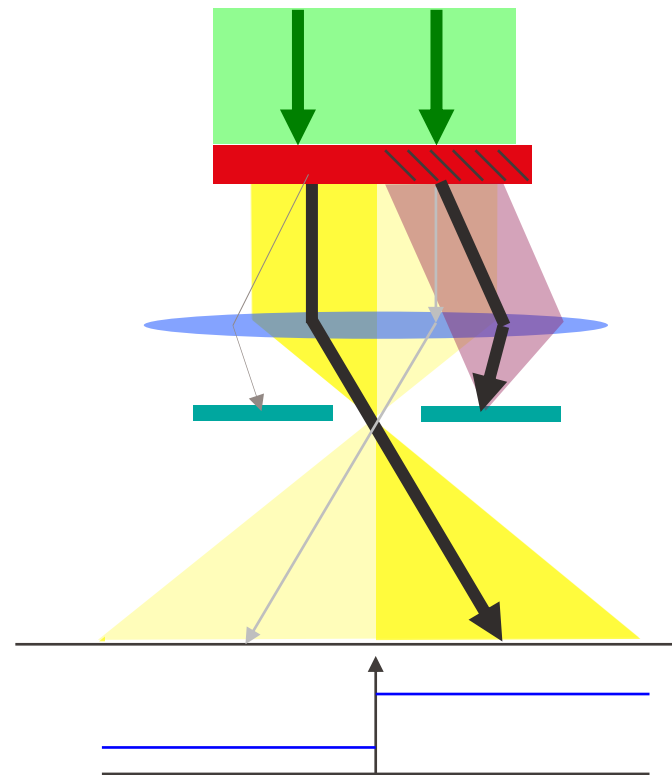


Path difference between reflection
from planes distance d_{hkl} apart
 $= 2d_{hkl} \sin\theta$

$$\text{Bragg law: } \lambda = 2d_{hkl} \sin\theta$$

→ Bragg diffraction at angle 2θ

Diffraction contrast



TEM gives image & diffraction information!

Principle of diffraction contrast imaging:

Typically we use an objective aperture to select either the direct beam or a specific diffracted beam in the back-focal plane.

If the diffraction condition changes across the sample the intensity in the selected beam changes; the intensity in the image changes correspondingly.

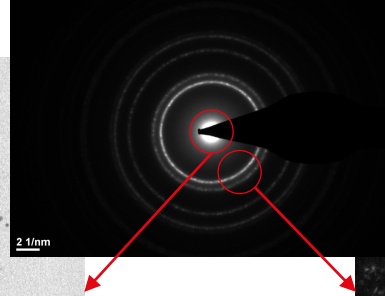
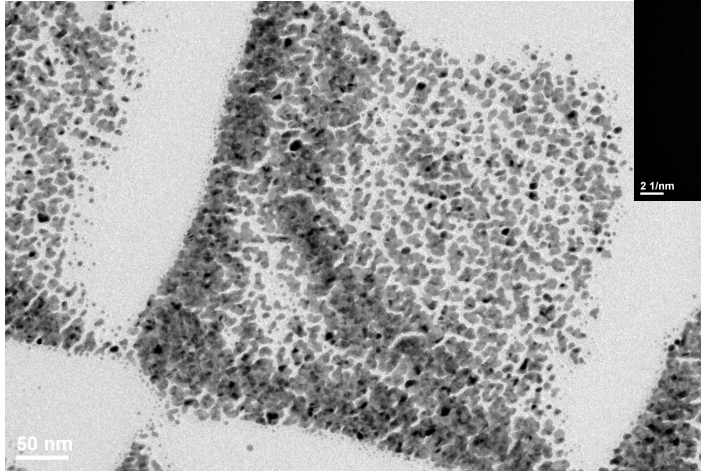
In other words we make a spatial map of the intensity distribution across the sample in the selected beam: *it is a mapping technique*.

In this way we can image changes in crystal phase and structural defects such as dislocations

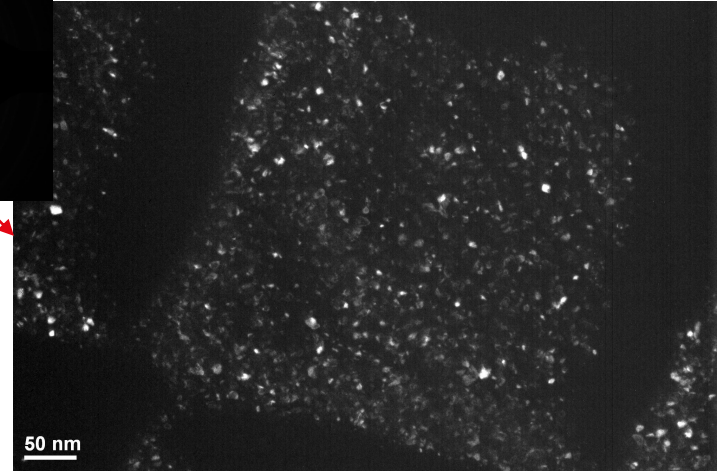
As an example such TEM imaging was a key piece of evidence proving the existence of dislocations

EPFL Diffraction contrast imaging

Bright-field image



Dark-field image

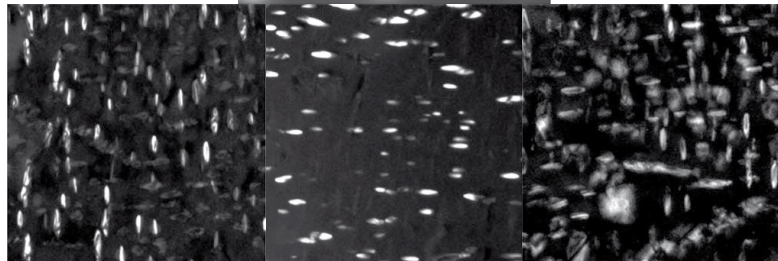


- Strongly diffracting crystals: dark
- Removes ghost image

- Only crystals strongly diffracting into objective aperture: bright
- Possibility of crystal phase/orientation discrimination

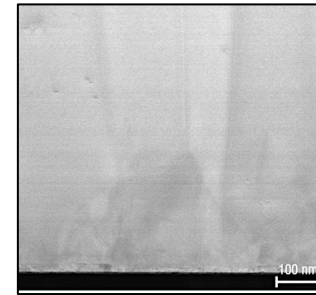
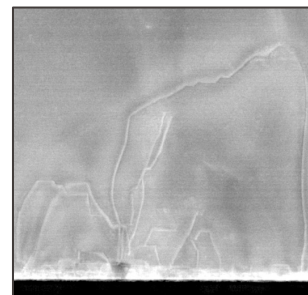
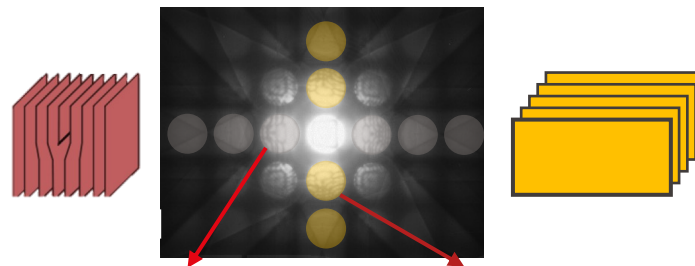
Map intensity in the diffracted beam

Crystal phase/orientation discrimination



Al-alloy containing precipitates with preferential growth direction

Crystal's defect imaging/analysis



Dark-field images of dislocations in GaN thin film on sapphire

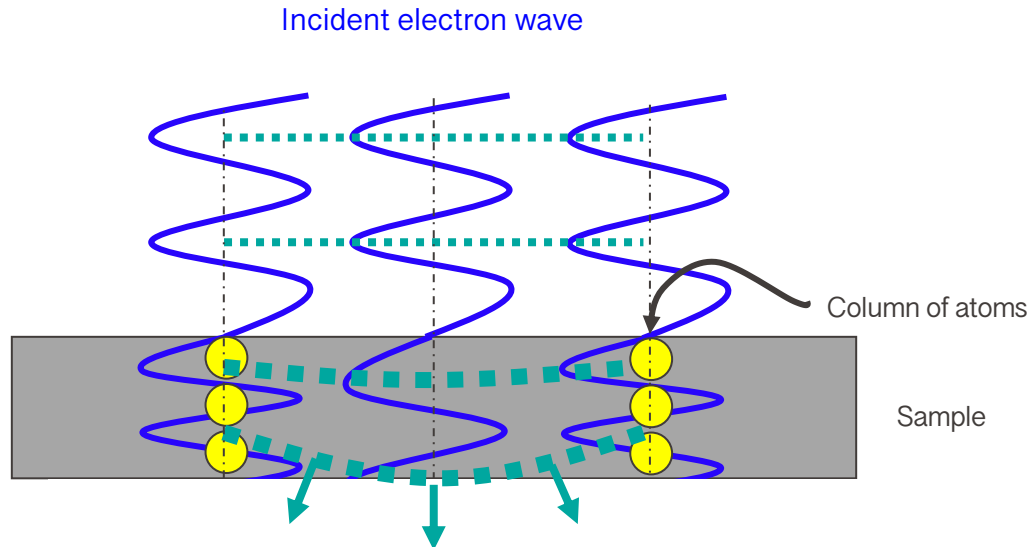
▪ Image formation in TEM

- Image and diffraction modes
- Bright- and dark-field modes
- High-resolution TEM

▪ Image contrast in TEM

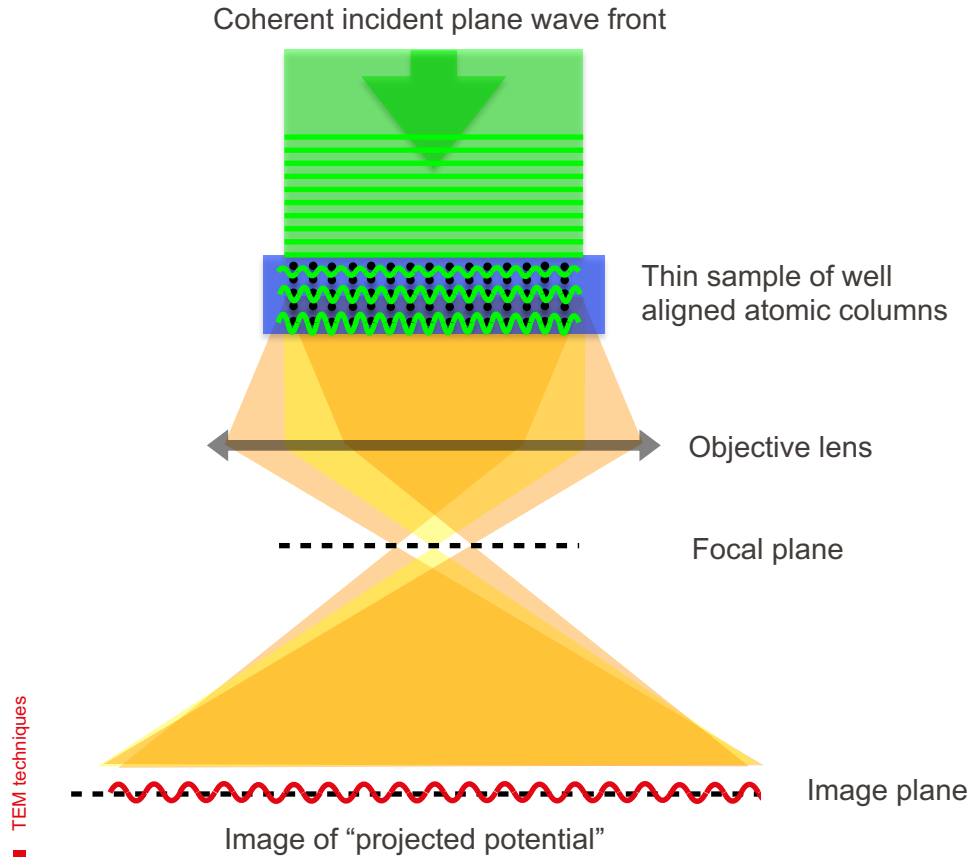
- Mass-thickness contrast
- Diffraction contrast
- Phase contrast

What happens when an electron wave passes through the sample?

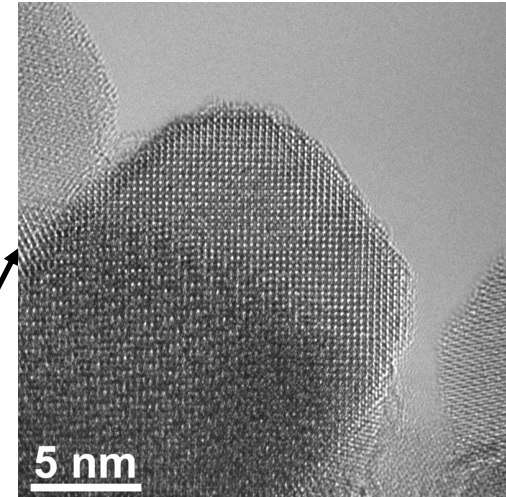


Variations in the projected potential produce local relative phase shifts of the electron wave. The wave front therefore bends as wave travels through medium.

The direction of propagation of the electron may change! $\Rightarrow$ Diffraction!



Due to changes in sample thickness and orientation, as well as lens imperfections, image interpretation is complex.



Lattice fringes in iron oxide nanoparticles

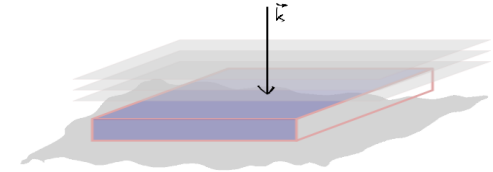
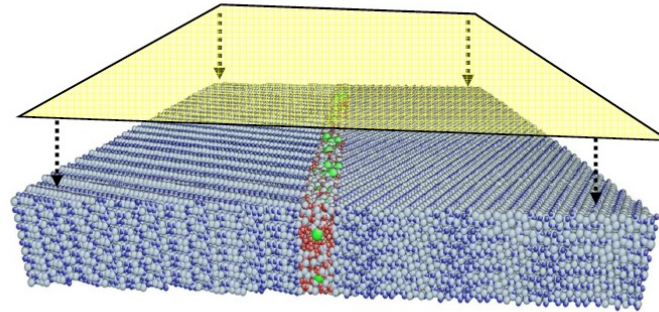
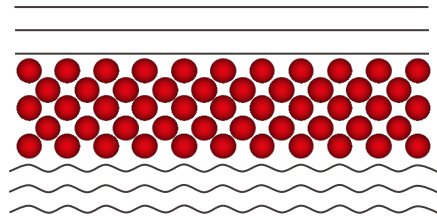
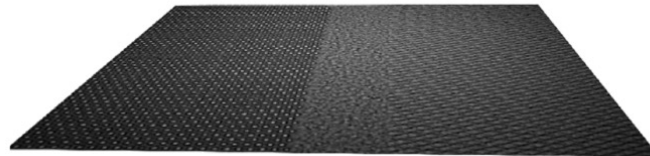


Image forming lens

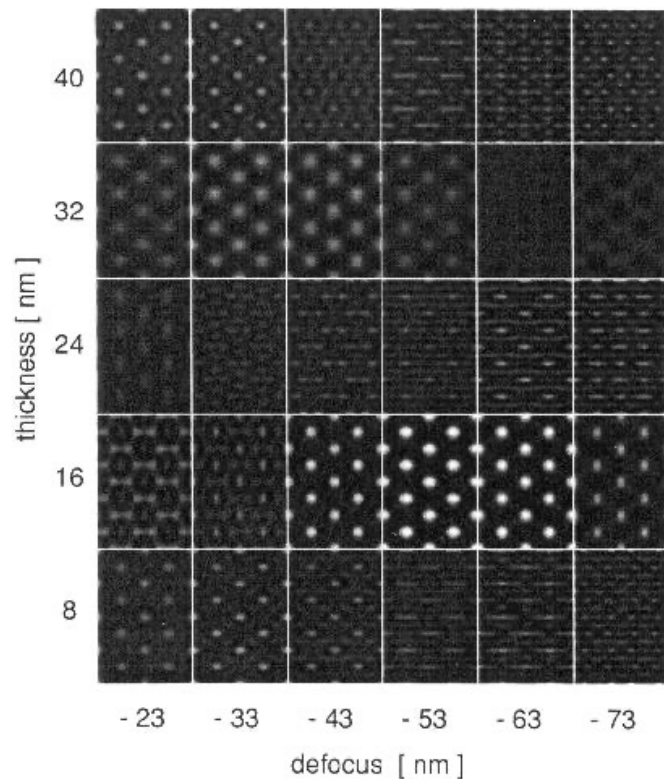
But ...
not a perfect lens!



HR-TEM can give you local structural information of your specimen. However, do not expect straightforward interpretation.

Resist the temptation of interpreting the spots as atoms!

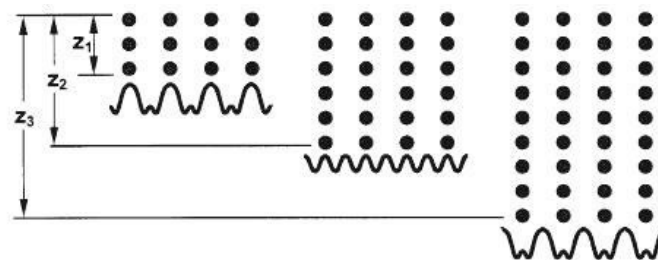
Phase contrast images can be difficult to interpret, because many factors contribute to phase shift:
Thickness, orientation, scattering factor, focus, spherical aberration



Resist the temptation of interpreting the spots as atoms!

The crystal potential serves to phase shift the electron wave locally; and crystal thickness affects phase shifts.

Thus at the crystal exit surface, the electron wave carries information about the crystal potential, projected in the direction of the incident beam.



The objective lens (CTF) determines how much phase signal gets transmitted to the real space wave-function in the image plane.

Mass-Thickness contrast

- Applies for both crystalline and amorphous phase

Diffraction contrast

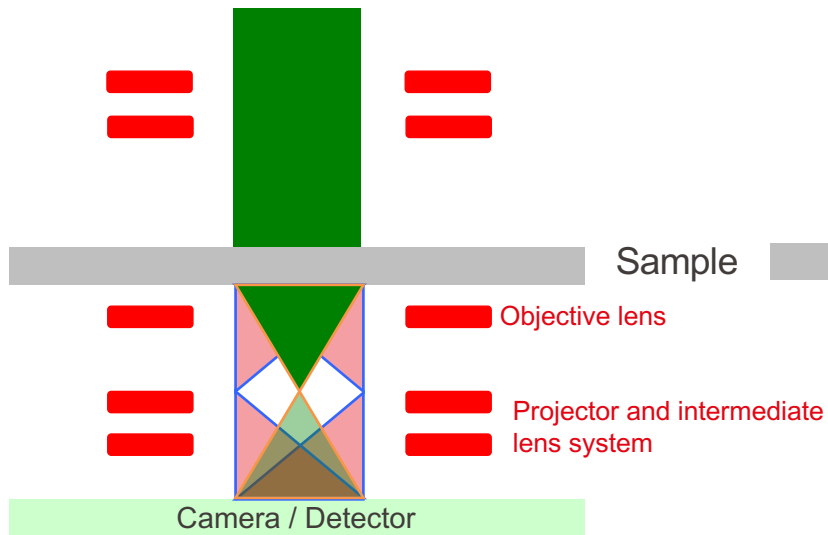
- Bright-field: objective aperture centered on “unscattered” beam
- Dark-field: objective aperture centered on “diffracted beams”

HR-TEM Phase contrast

- Developed by the interference of two waves, one which undergoes a phase shift due to the interactions with the sample crystal structure of a given thickness and is altered by the microscope aberrations
- Simulations are needed to interpret phase contrast images properly

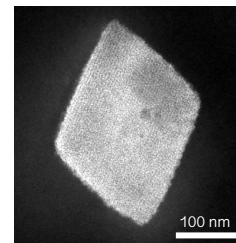
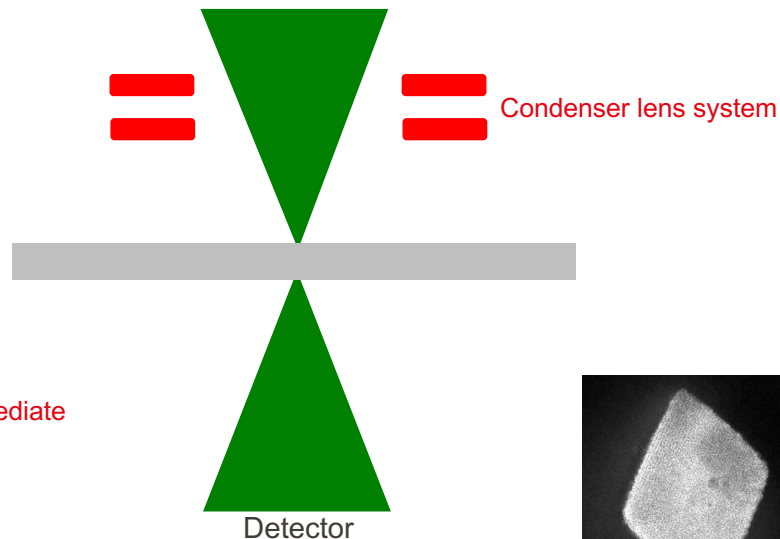
Conventional TEM

Electron beam (60-300 keV)

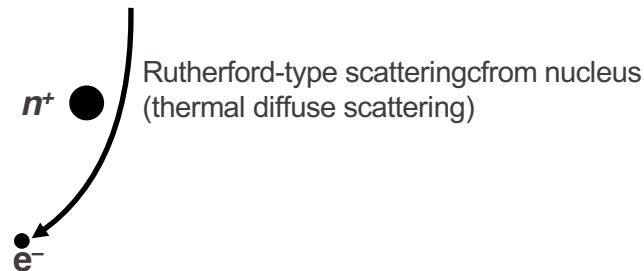
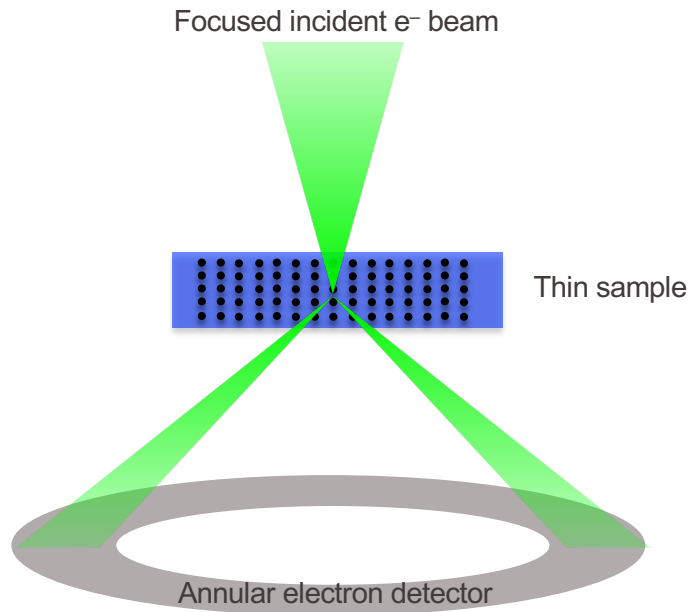


Scanning mode (STEM)

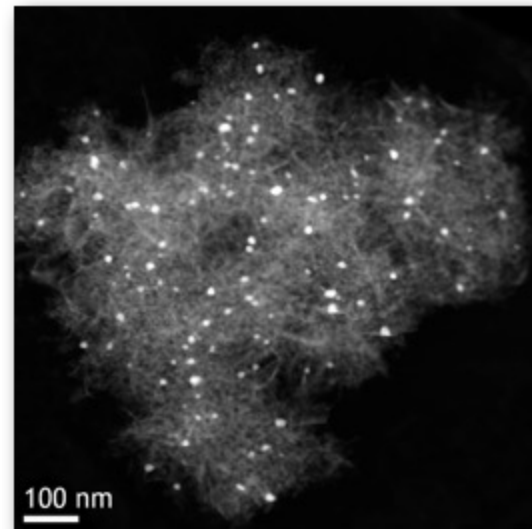
Electron beam (30-300 keV)



2D projection of a 3D object

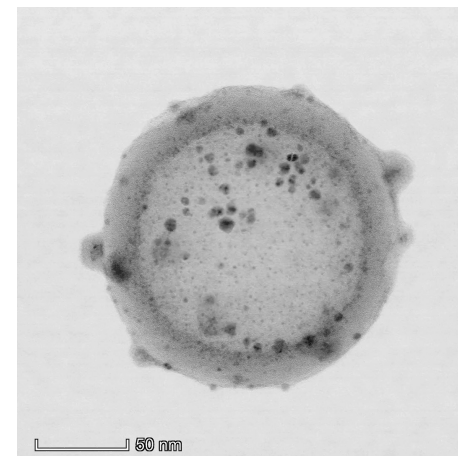
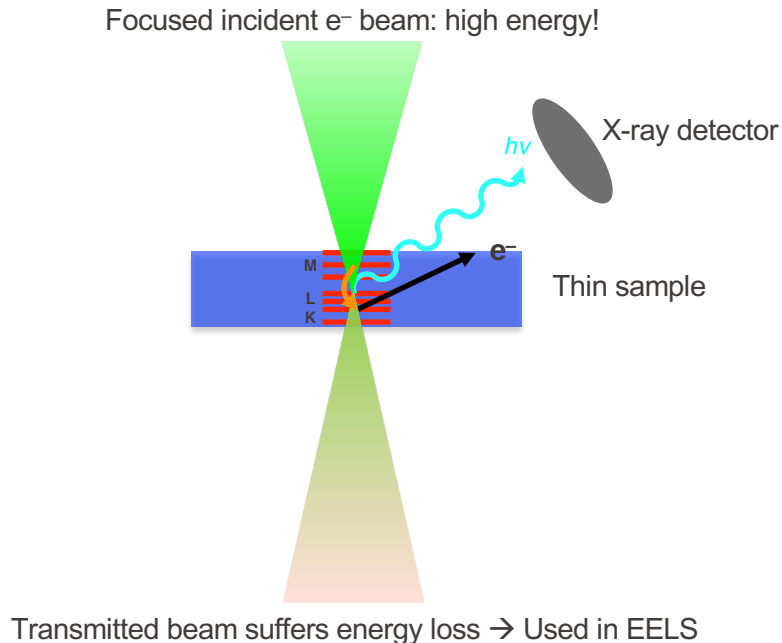


High-angle annular dark-field (HAADF) image

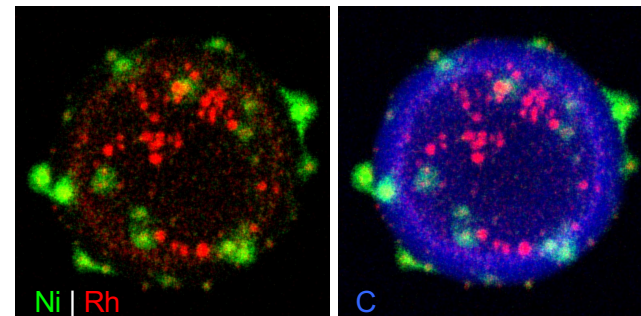
Pt catalyst particles on Al_2O_3

Mass/thickness contrast image

- Incoherent Rutherford-type scattering deflects transmitted e^- to high angle of scattering
- Larger nucleus / thicker the specimen $\rightarrow$ More scattering
- Map image intensity as function of probe position (x, y)
- Image intensity: $I(x, y) \propto t * Z^{1.6-2}$



Ni-Rh catalytic nanoparticles in carbon shell



Map X-ray intensity as function of probe position (x,y)

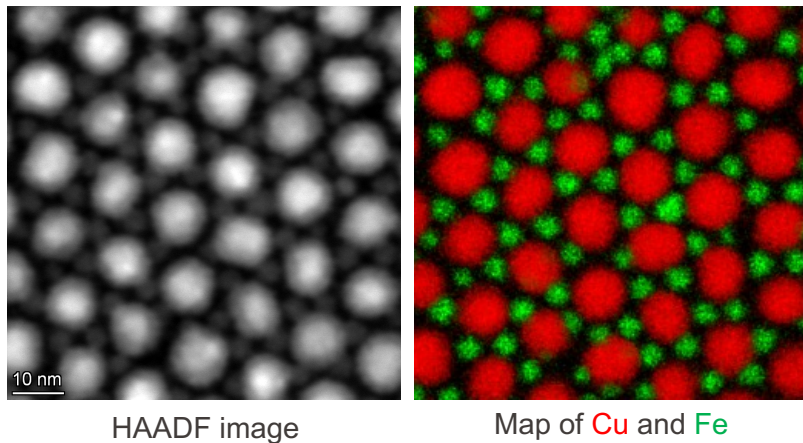
- High energy incident electrons (ballistic) $\rightarrow$ Ejection of inner shell e^-
- Upper shell e^- descends
- Transition energy emitted as X-ray;
Characteristic of element | $E_{X\text{-ray}} = E_{\text{Upper shell}} - E_{\text{Inner shell}}$

With fast mapping STEM-EDX has become a regular feedback tool for materials synthesis

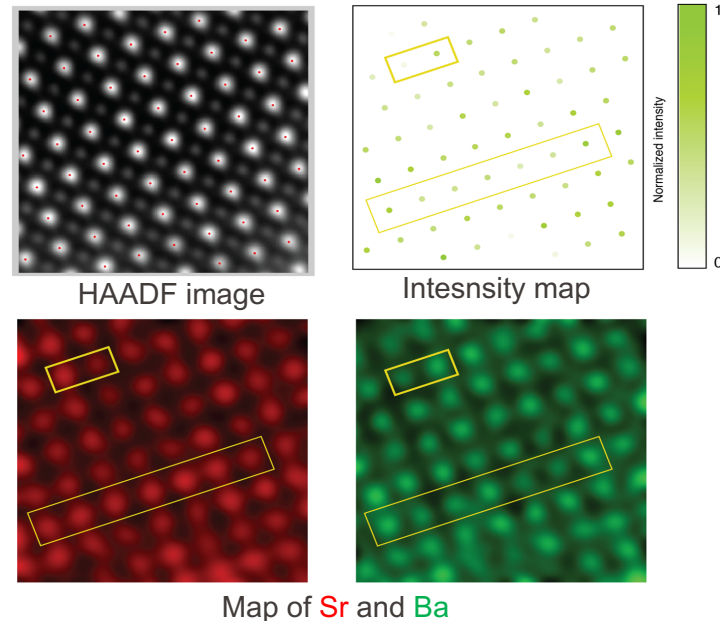
Sample characterized in a couple of minutes/hours

With aberration-corrected STEM, atomic resolution EDX became possible

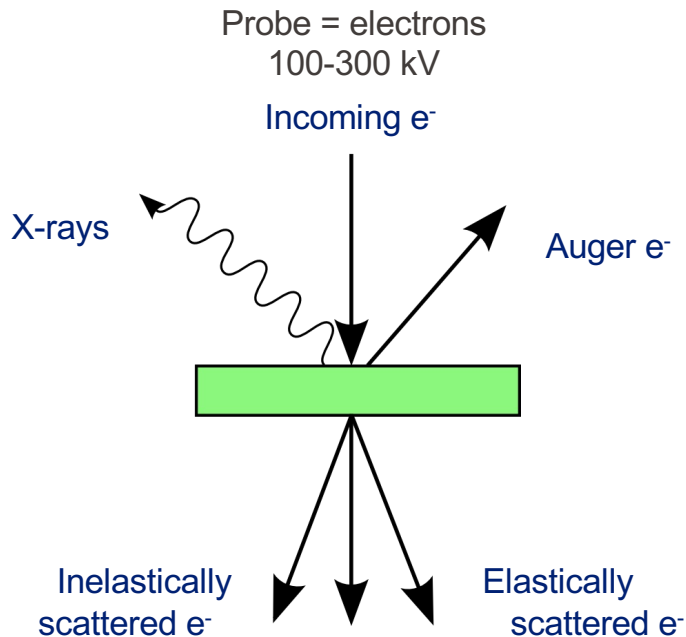
Example : Assembly of Fe_3O_4 and Cu particles



Example: $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$

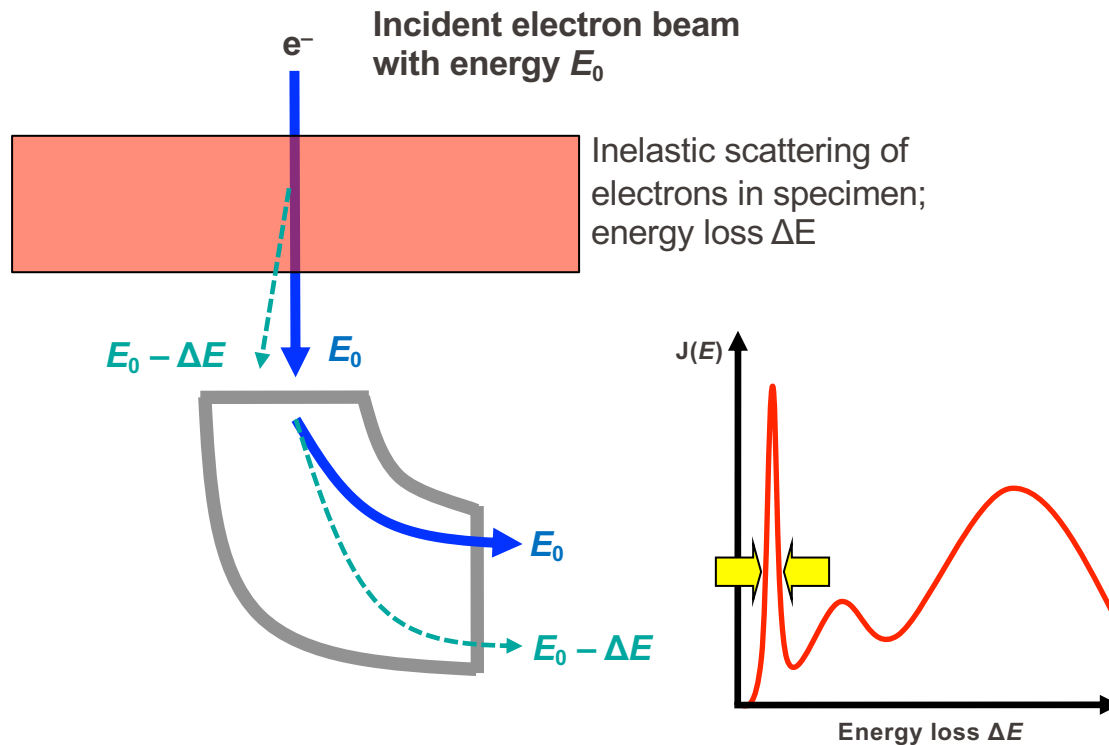


The TEM specific microanalysis technique!

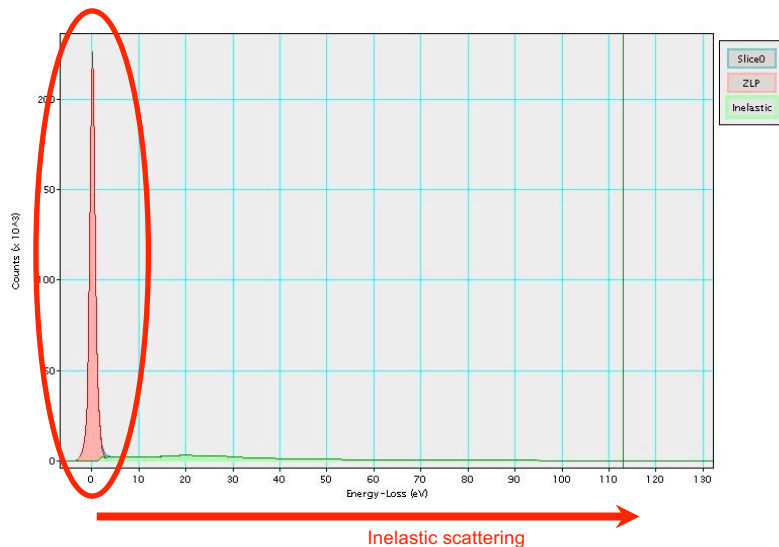




e.g. Gatan Enfina



Magnetic prism separates electrons with different energy; produces spectrum of intensity $J(E)$ vs energy loss ΔE : **The energy-loss spectrum**

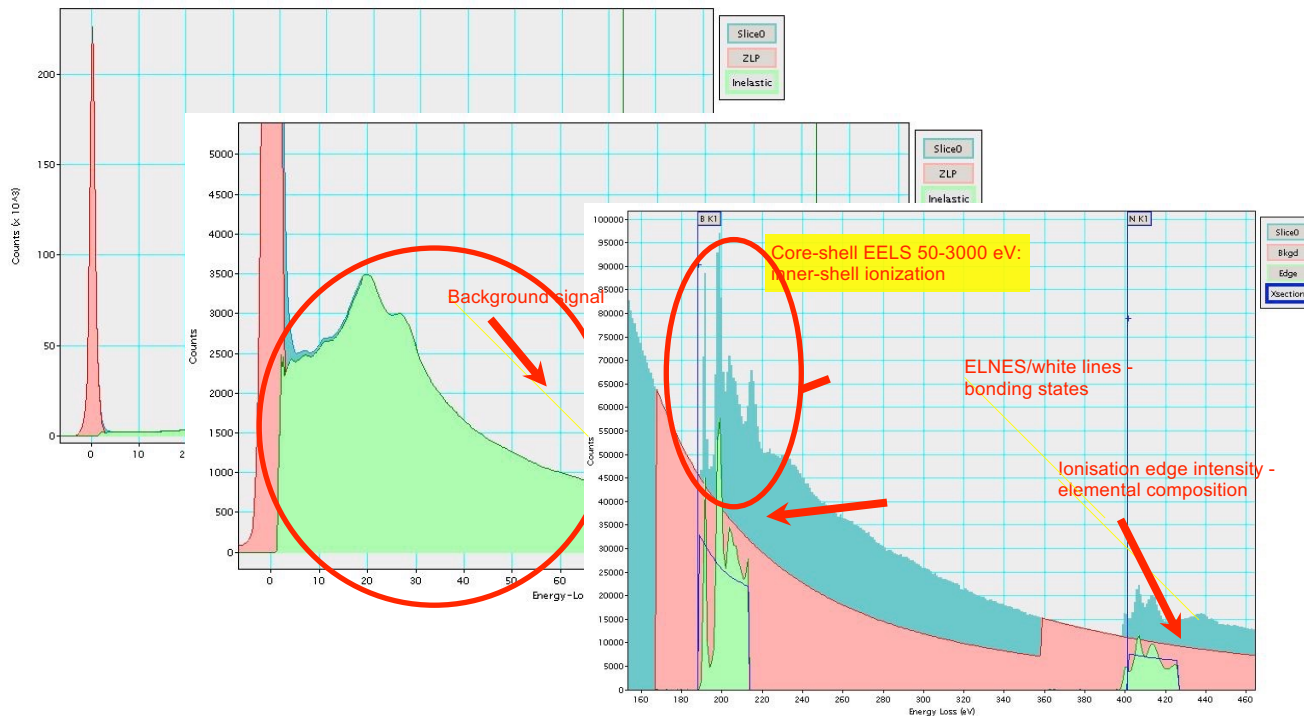


Zero-loss: Elastically-scattered e^-
Information about specimen thickness



Interaction with outer electrons (conduction/valence)

Low-loss spectrum 0-50 eV: valence excitations - plasmons (bulk & surface), band gaps, optical properties



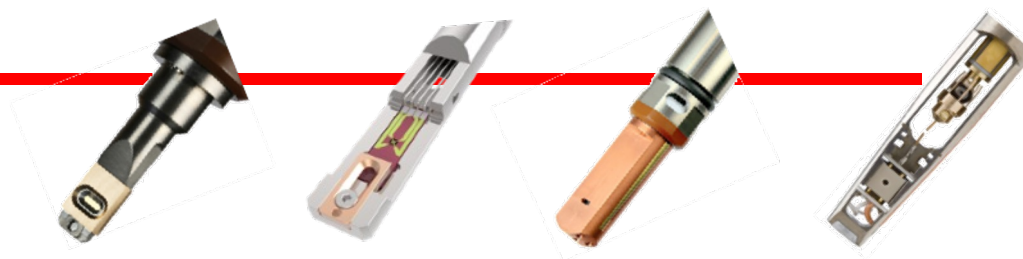
Interaction with core electrons

Core-loss spectrum 50-3000 eV: inner shell ionization

ELNES/white lines: Bonding state

Ionisation edge intensity: elemental composition

Stimuli	Possible techniques	Information
• gas • liquid • temperature • magnetic field • current/voltage • mechanical load • light • ...	• (S)TEM imaging • diffraction • electron energy-loss spectroscopy • energy-filtered TEM • energy-dispersive X-ray spectroscopy • Lorentz microscopy • holography • ...	• microstructure • crystallography • chemistry • diffusion/migration • optical properties • electric fields • magnetic fields • ...



Different dedicated holders

Liquid phase processes

- Hydration and other liquid phenomena
- Crystal growth from the liquid phase
- Corrosion

Phase transformations

- Solid state phase transformations
 - Crystallization and melting
 - Structural transformations
 - Solid state reactions
- Solid state transformations in nanostructured materials
 - Size-dependent transformations in embedded nanoparticles
 - Shape and phase transformations in free-standing nanoparticles
 - Sintering of nanoparticles

Elastic and plastic deformation

- Microscopic phenomena during plastic deformation
 - Deformation of polycrystalline materials
 - The effect of gas environment on deformation
 - Grain boundary motion
 - Deformation phenomena in single crystals
 - Deformation of multilayers
- Relaxation of epitaxially strained materials
- Mechanical properties of nanostructures, thin films and surfaces
 - In situ indentation and straining of thin films
 - Mechanical properties of nanostructures
 - Surfaces: Tribology and Nanomanipulation

Surface reactions and crystal growth

- Modification of surface structure
- Oxidation and other chemical reactions at surfaces
- Growth of nanostructures
 - Carbon nanotubes
- Thin film growth and defect formation
 - Epitaxial growth
 - Polycrystalline growth
- Crystal growth on patterned substrates

Domain wall motion and flux dynamics

- Magnetic domain switching
- Flux motion in superconductors
- Switching phenomena in ferroelectrics

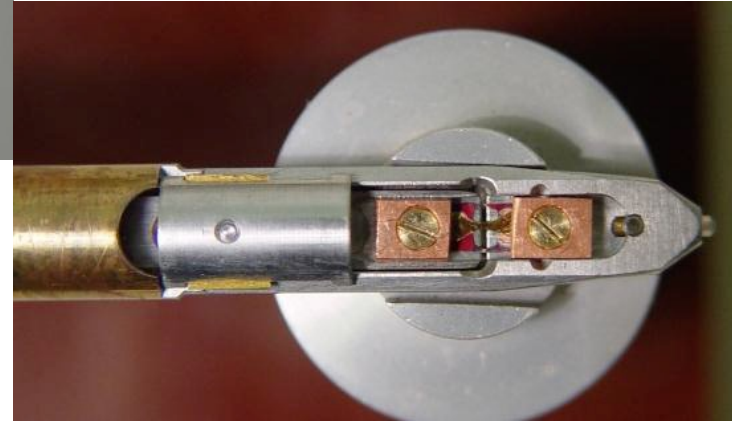
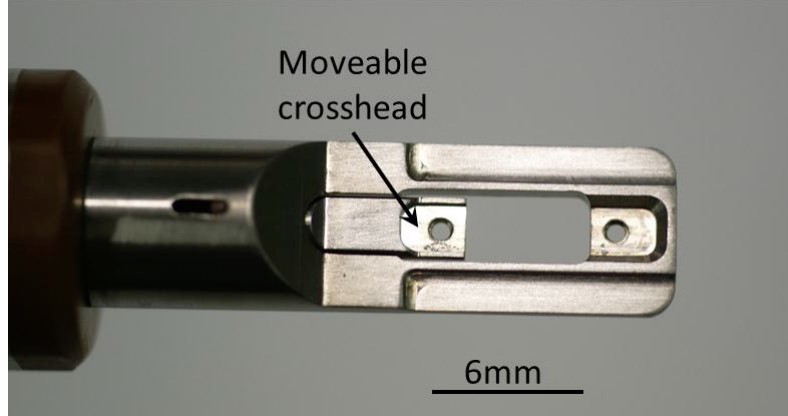
Correlation of structural and electronic properties of materials

- Electrical measurements on TEM samples: samples as devices
- Electrical measurements on individual nanostructures

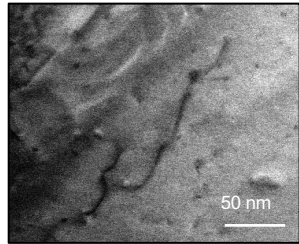
Beam induced processes

- Electron beam induced phenomena
 - Interaction with the vapour above the specimen
 - Formation of point defects
 - Beam induced transformations, surface reactions, growth
 - Radiation enhanced dislocation motion
- Hole drilling
- Ion implantation
 - High energy ion accelerators
 - FIB in the TEM

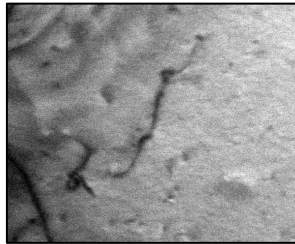
Conventional straining holder



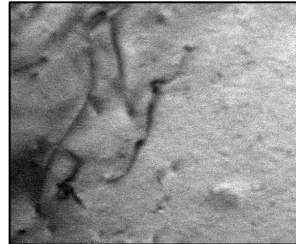
Dislocations interaction
Specimen: Cu foil | *in situ* deformation



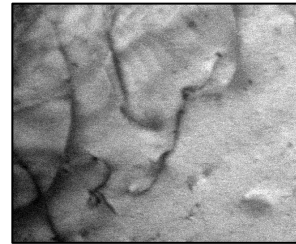
t_0



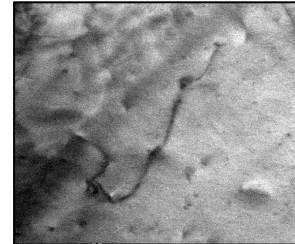
t_1



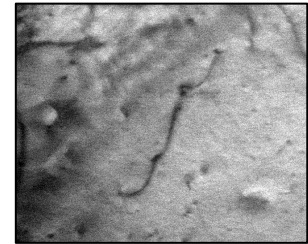
t_2



t_3

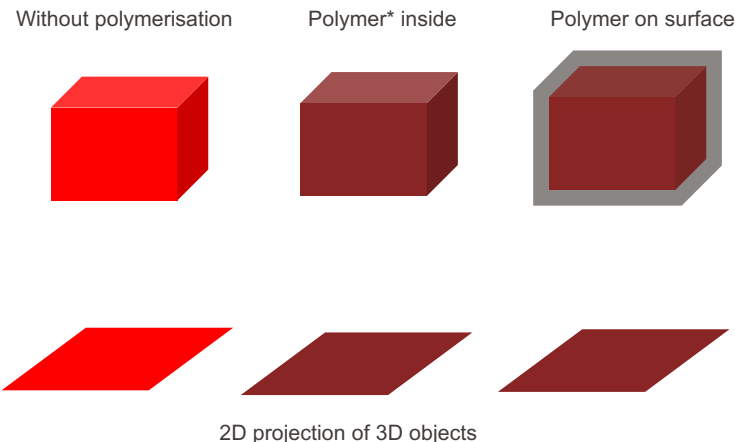
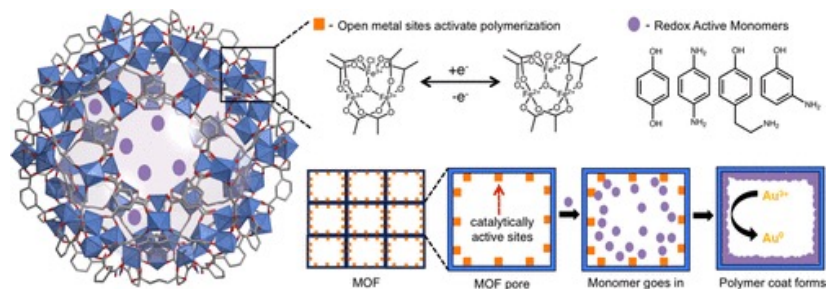


t_4

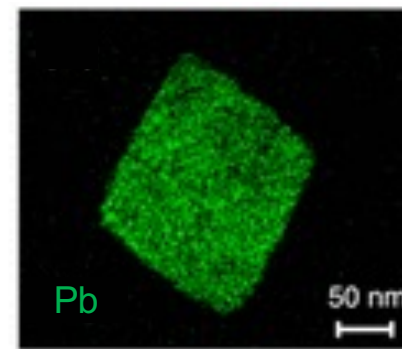
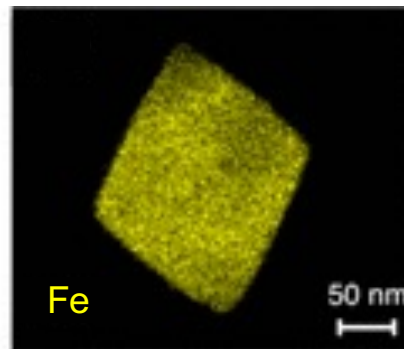
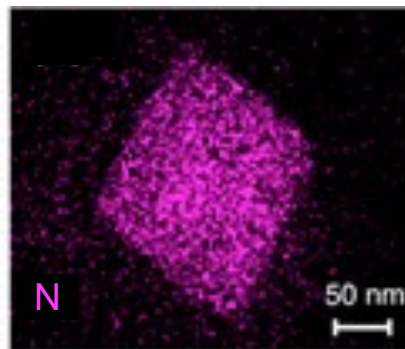
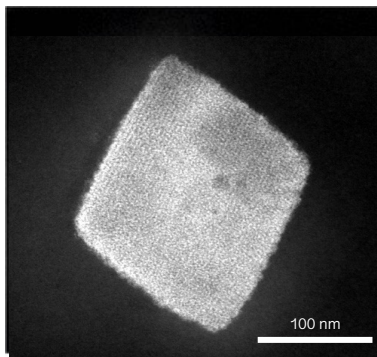
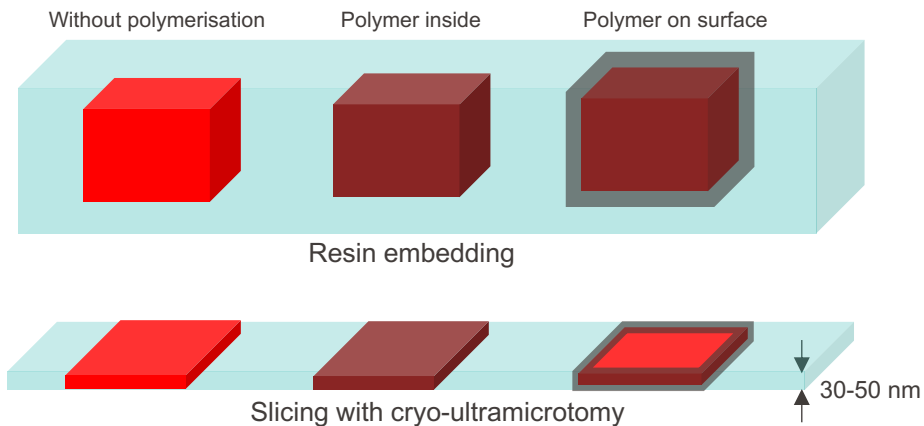


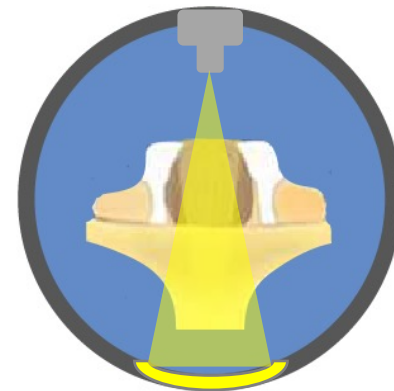
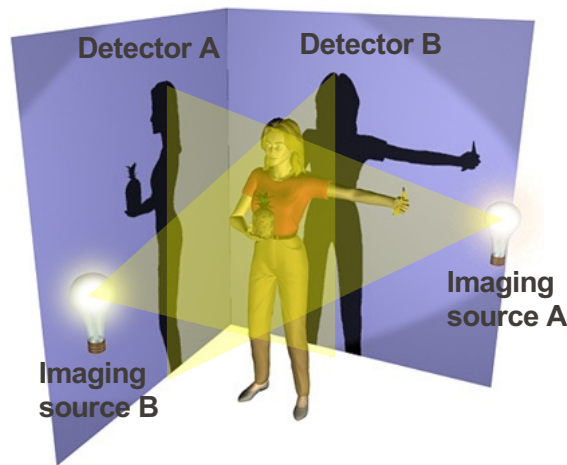
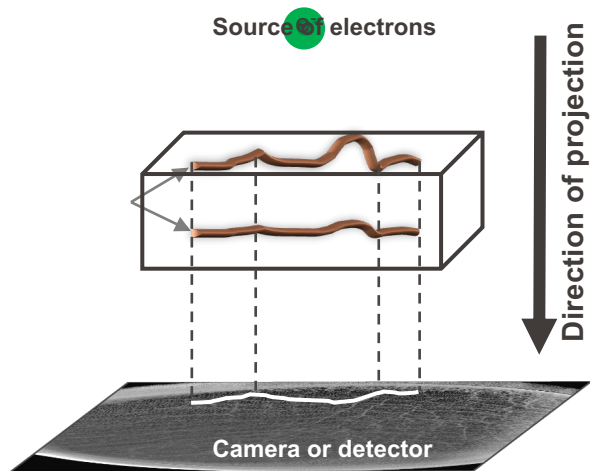
$t_5 = 16 \text{ Sec}$

- A window into the behavior of materials under real processing conditions.
- A continuous view of a process, which may take the place of multiple post-mortem measurements.
 - It is easier to catch a transient phase or observe a nucleation event.
 - Specific and detailed kinetic information, such as the motion of individual dislocations under known stress, or growth rates of individual nanocrystals.
- But this unique information comes at the cost of increased experimental complexity.
- Expensive: machine time, holders



**Due to projection problem,
not possible to determine whether the polymer is inside the particle or on its surface**





X-ray Computed tomography (CT) scan

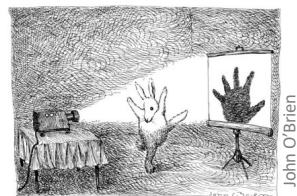
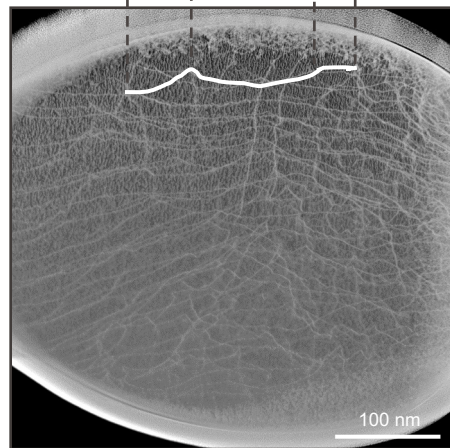
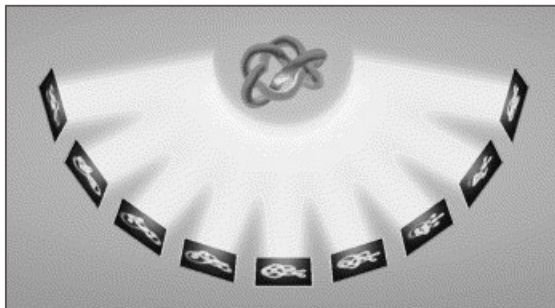
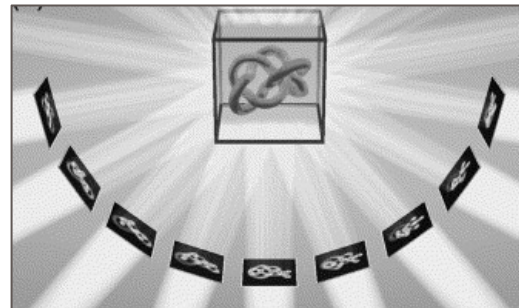


Image is the projection of a 3-D object onto a 2-D plane

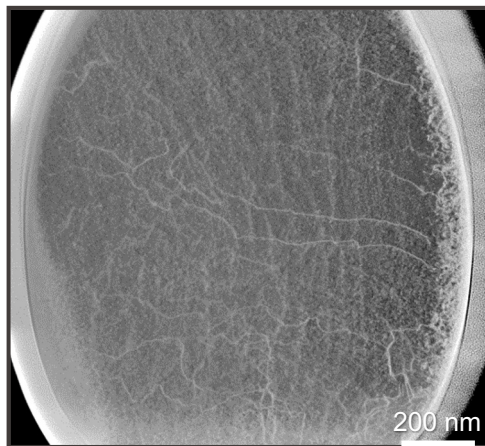




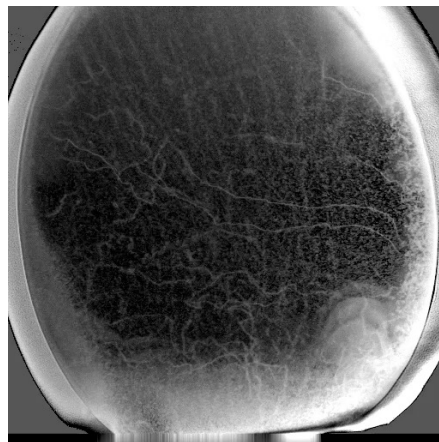
Series of projections



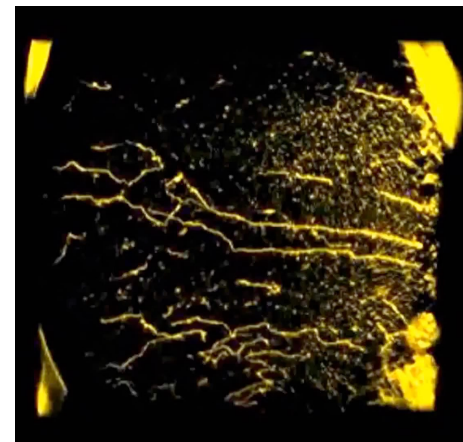
Back-projection



2D image



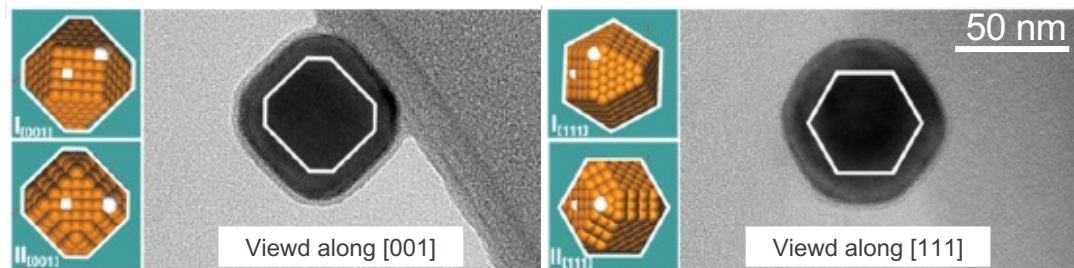
Series of tilted images
-35°/+35° tilt arc | 1° interval



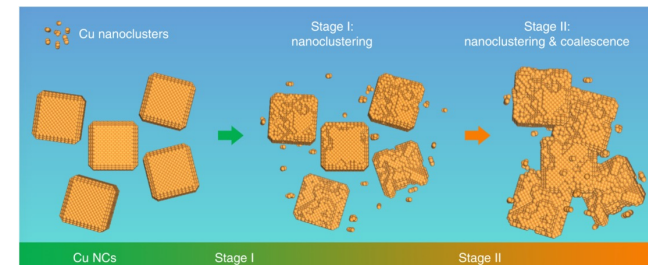
3D reconstruction
SIRT 30 iterations

EPFL ■ Electron microscopy to study degradation process of Cu NPs

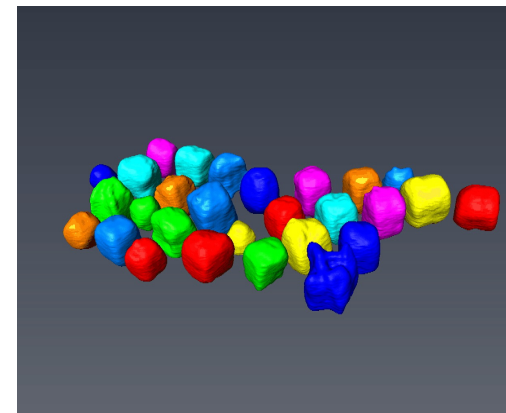
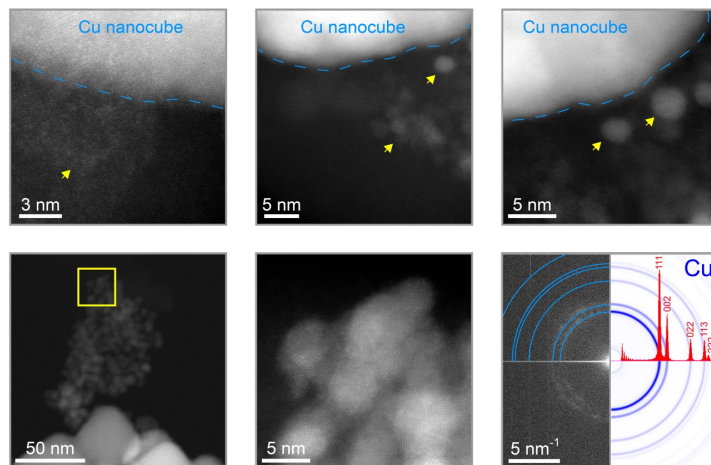
Advanced microscopy techniques and image simulation enabled researchers to uncover potential-driven nanoclustering degradation pathway Cu nanocubes during electrochemical CO₂ reduction.



Determination of dominant facets in Cu NC by electron imaging



Followed morphological evolution during operation and correlate it with the electrocatalytic performance

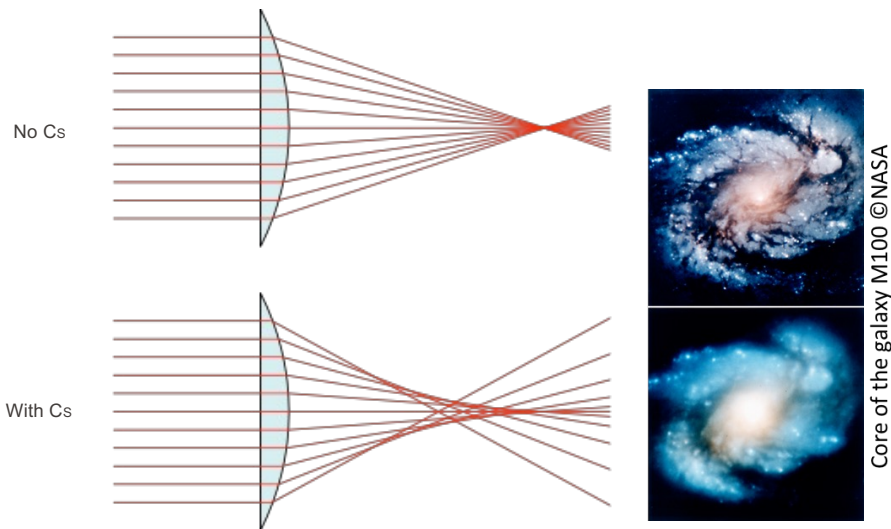


Determination of morphological changes using electron tomography

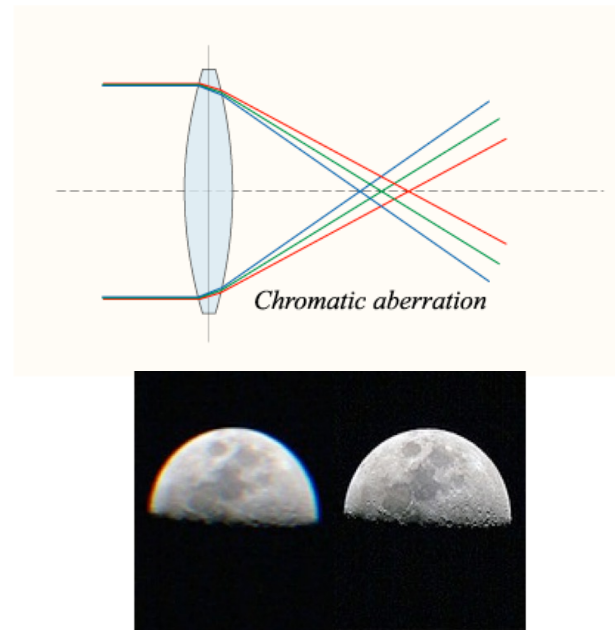
Electromagnetic lenses in TEM column are toroidal

Lenses inherently convergent

→ Spherical aberration (C_s) and Chromatic aberration (C_c)



Parallel rays that pass through the central region of the lens focus farther away than the rays that pass through the edges of the lens. Results in multiple focal points and thus a blurred image.

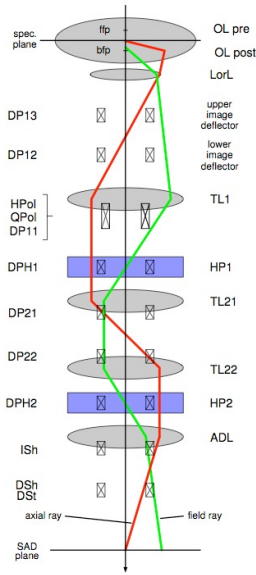


Lens cannot focus all energies (wavelengths) to the same convergence point.

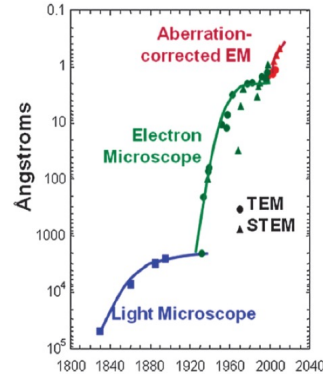
Combination of standard radially-symmetric convergent lenses with multipole divergent lenses (e.g. tetrapoles, hexapoles) to tune C_s

Like “glasses” for TEM (or the Hubble)

→ Resolution jumps to sub-Å!



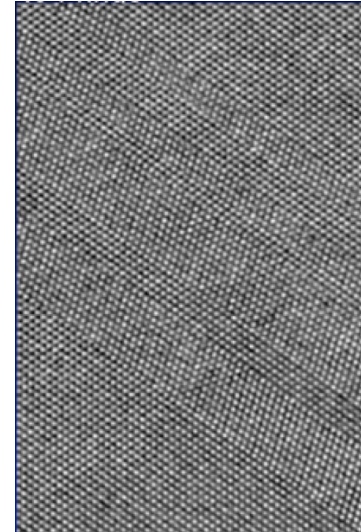
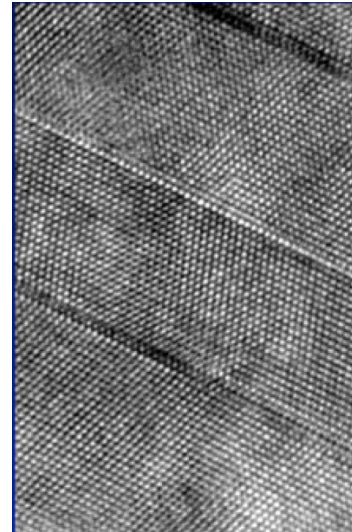
CEOS corrector



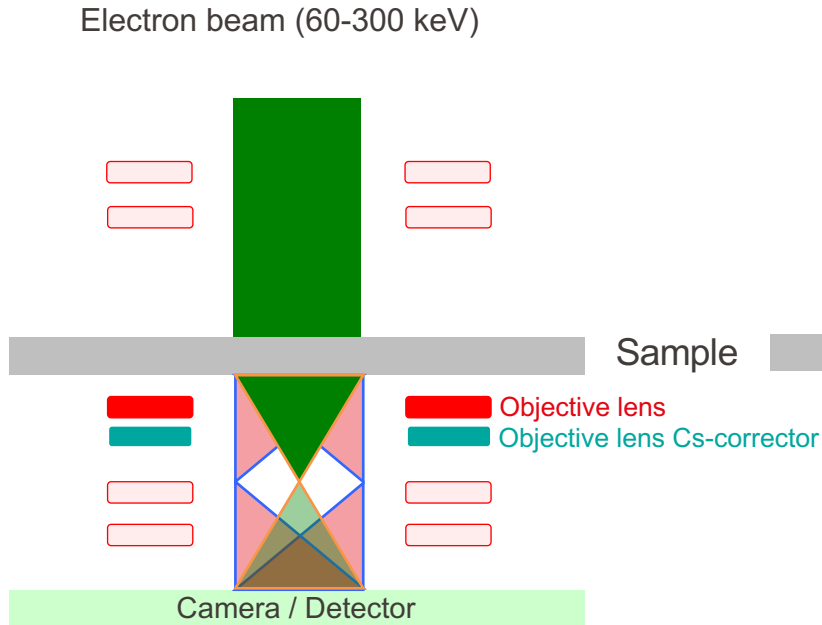
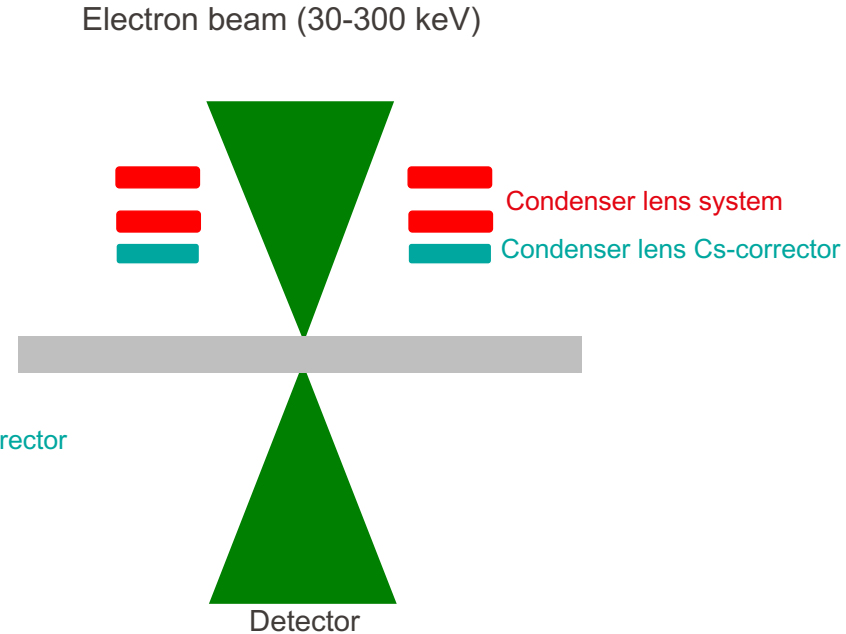
Example: $\Sigma 3$ grain boundaries in Al

Uncorrected

Cs-corrected



Images: Oikawa, JEOL

TEM (Image-corrected)STEM (Probe-corrected)

A double Cs-corrected S/TEM has both image and probe correctors

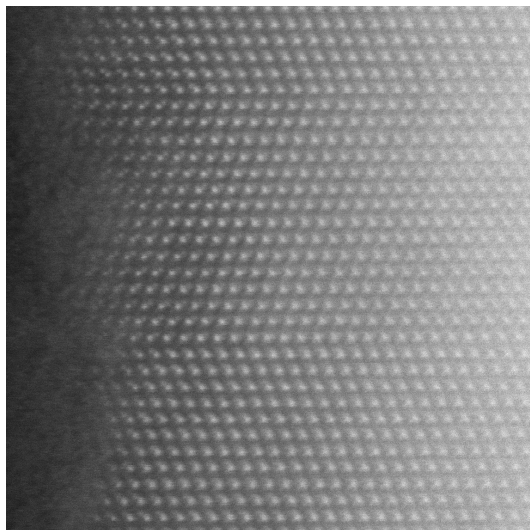
Example: (Al)GaAs nanowires imaged at 300 kV in STEM mode

HR-STEM with sub-Å Cs-corrected probe:

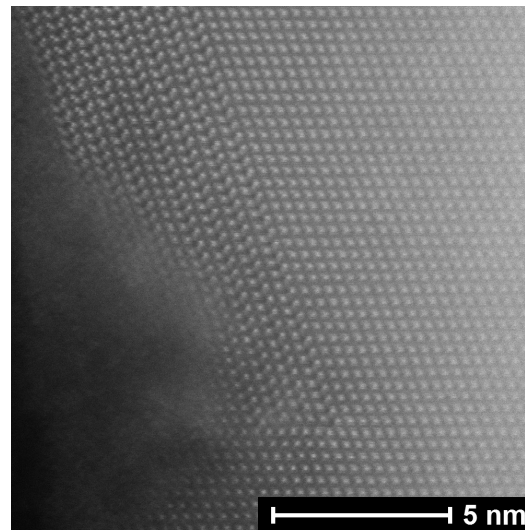
- Simple (quantitative) atomic column contrast

- Reduced sensitivity to small changes in sample orientation

- Image either in focus or out of focus (no contrast reversals with defocus, thickness)

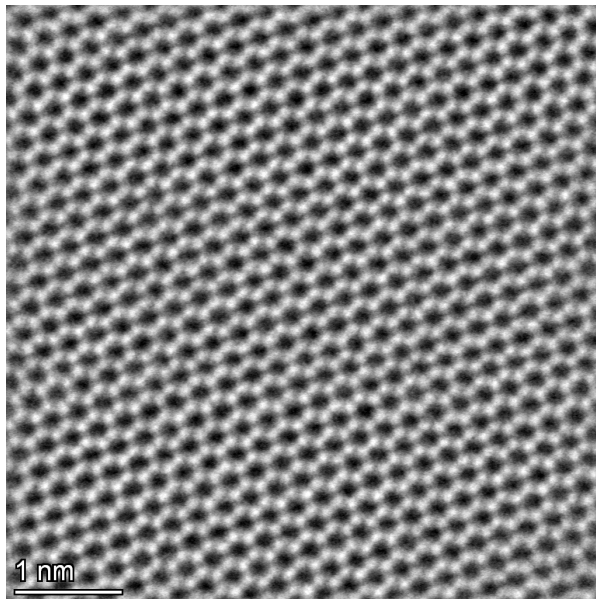


FCC twinning



HCP inclusion and dislocation

- Cs-correction and monochromatic illumination to reduce Cc allow sub-Å resolution even at lower kV where electron wavelength λ is greater
- Beam sensitive, low contrast materials can be imaged
- Here a monolayer graphene is imaged with 80 keV in STEM mode (IDPC)



TEM is now not one technique that can be easily summarised, but is split into many specialisms. In essence this is due to the many types of interaction of the electron beam with the atoms of a sample.

Modern TEM instruments are arguably the most versatile analytical tools. Many other possible uses (e.g. imaging of magnetic domains, optical plasmon mapping, in-situ studies) exist..

Aberration-correction and improved instrument stability give sub-Å resolution in TEM and STEM. With lower beam voltages lighter elements can be analysed without beam damage.

Faster, more sensitive spectrometers give unprecedented access to composition, chemistry and physics of materials.

Computer interfaces and software allow acquisition and processing of large datasets.

With the latest instrumentation, the sample and specimen preparation are often the limiting factor!

Some useful literature

Transmission Electron Microscopy by D.B. Williams and C.B. Carter (Springer)

Large Angle Convergent Beam Electron Diffraction by J.-P. Morniroli

Aberration-corrected imaging in transmission electron microscopy: an introduction by R. Erni

Scanning Transmission Electron Microscopy by S.J. Pennycook and P.D. Nellist (eds) (Springer)

Diffraction Physics by J.M. Cowley (North Holland/Elsevier)

Science of Microscopy by C.W. Hawkes and J.C.H. Spence (eds) (Springer)